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# FAST EV CHARGING - 25KW SiC REFERENCE DESIGN

Didier Balocco  
EMEA Business Marketing Engineer

**WÜRTH ELEKTRONIK** MORE THAN YOU EXPECT

# DIDIER BALOCCO

## ■ Diploma :

- Engineering degree from "École Nationale Supérieure d'Électronique et de RadioÉlectricité de Bordeaux", France in 1992
- Ph.D. degree in Power Electronics from the University of Bordeaux in 1997.

## ■ Experience :

- Research engineer for dc-dc, ac-dc and dc-ac converters for telecom equipment and solar from 1 W to 150 kW from 1996 to 2014.
- Field Application Engineer (FAE) supporting South of France, Spain and Portugal in Fairchild Semiconductor from 2014 to 2016 and until 2018 with **onsemi**.
- EMEA Business Marketing Engineer in **onsemi** since 2018.





WÜRTH  
ELEKTRONIK  
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YOU EXPECT

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## FAST EV CHARGING – 25KW SIC REFERENCE DESIGN

- Introduction
- Review of the Key High-Power Blocks
  - 6-Pack, x-NPC, Vienna, DBC, LLC, CLLC, ...
- 25-kW building Block
- Why Modules ?
- Identified Sockets
- Measurement and Results
- Conclusion



# Review of the Key High-Power Blocks

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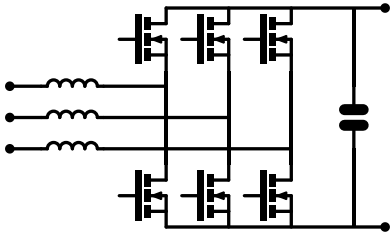
6-Pack, x-NPC, Vienna, DBC, LLC, CLLC, ...



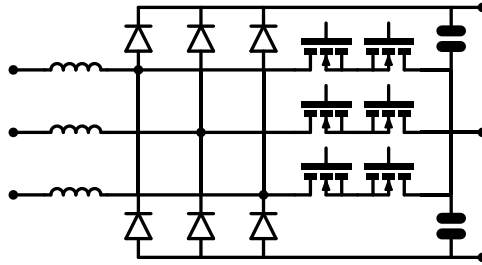
# TOPOLOGIES

## 3-phase Active Front End of PFC

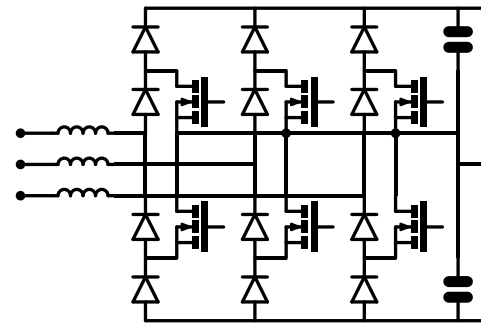
6 Pack Boost



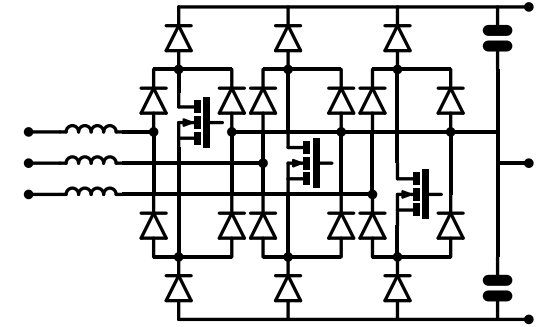
T-NPC Boost



NPC Boost

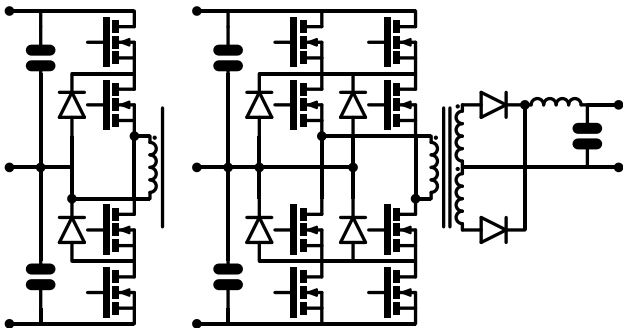


Vienna

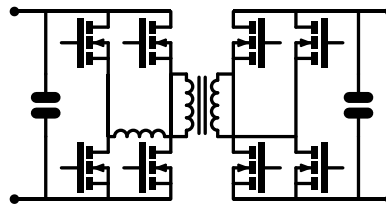


## Isolated DC/DC

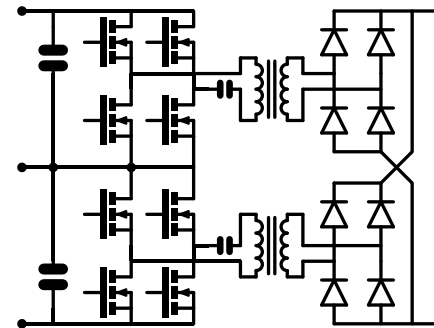
NPC Half-Bridge or Full-Bridge



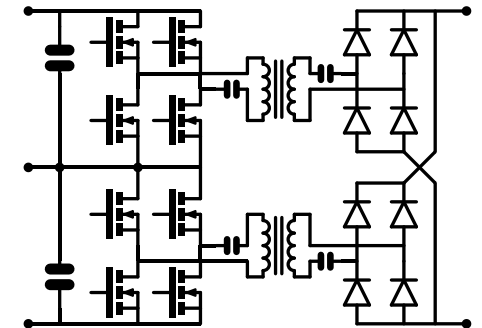
Dual Active Bridge  
(DAB)



Stacked LLC



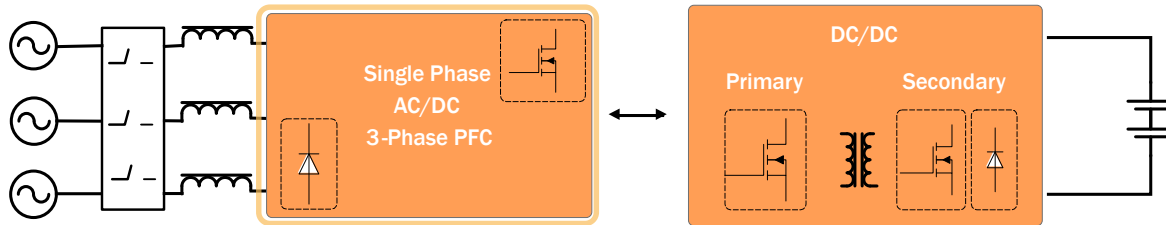
Stacked CLLC



# EV CHARGING STATIONS

## Active Rectification Stage or Active Front End (or PFC)

### ■ Vienna Rectifier Version

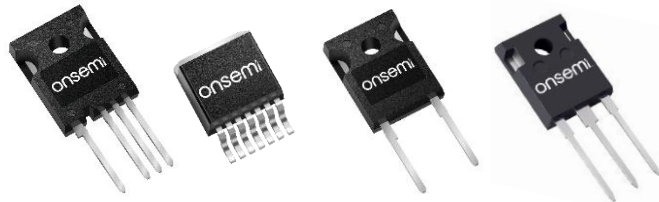
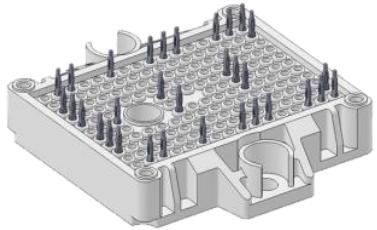


**Module**

F2 Vienna Rectifier

**Discrete**

SiC Diodes + SiC MOSFETs

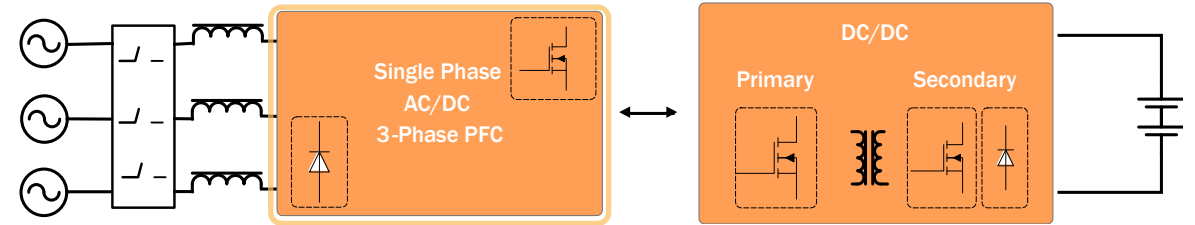


Robust

Avalanche Rated

High Efficiency

### ■ Six Switch Converter Version

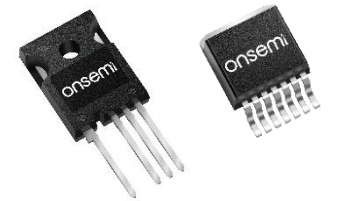
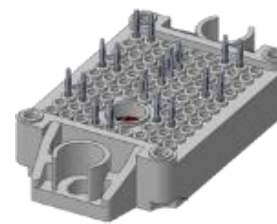


**Module**

F1 2-PACK Module

**Discrete**

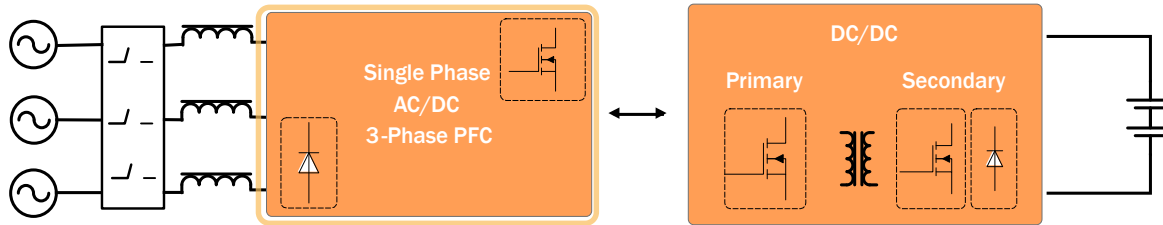
SiC MOSFETs



# EV CHARGING STATIONS

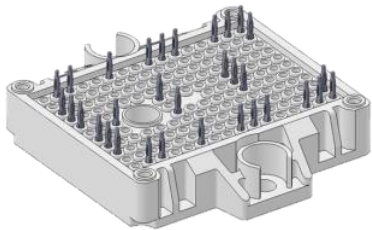
## Active Rectification Stage or Active Front End (or PFC)

### ■ Bidirectional TNPC Version



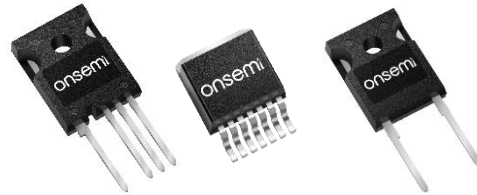
#### Module

F2 (Concept)



#### Discrete

SiC Diodes + SiC MOSFETs



Robust

Avalanche Rated

High Efficiency

### ■ Comments on bidirectional

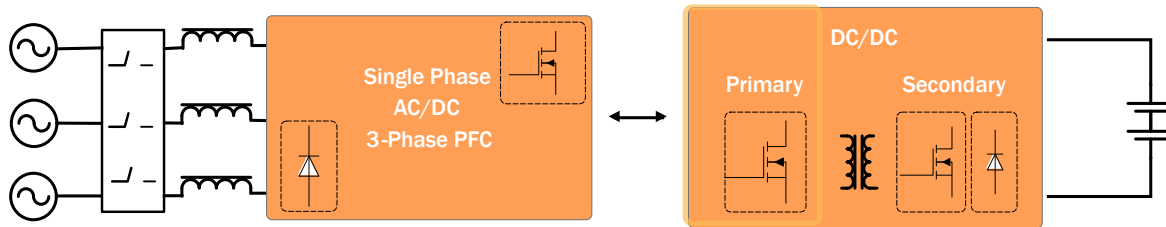
- Vienna: not bidirectional
- TNPC, Six switch: bidirectional

### ■ Where bidirectional is used

1. Provide reactive power support to grid.  
Often used where the maker of the EV charger is a utility.
2. Allow energy to be taken from car battery to grid.

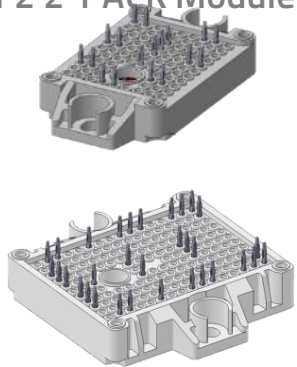
# EV CHARGING STATIONS – DC-DC STAGE

## ■ DAB, DC-DC, CLLC, ... Primary Stage



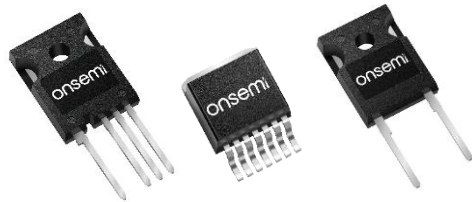
### Module

F1 2-PACK Module  
F1 4-PACK Module  
F2 2-PACK Module



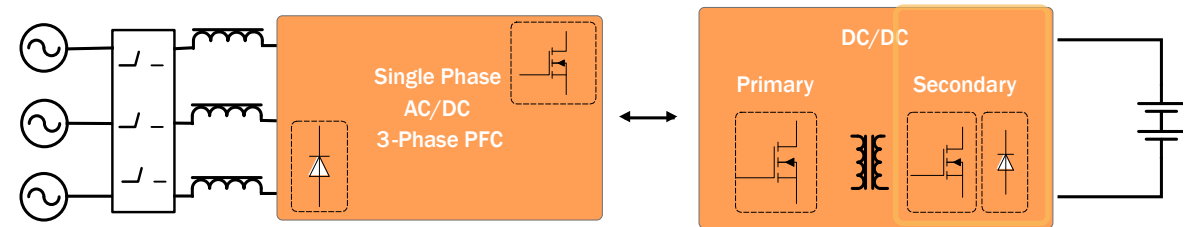
### Discrete

SiC Diodes + SiC MOSFETs



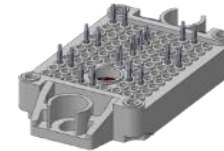
Robust  
Avalanche Rated  
High Efficiency

## ■ Diode Output Bridge



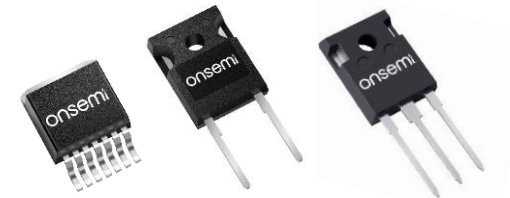
### Module

F1 4-PACK Module



### Discrete

SiC Diodes  
Single or Dual  
SiC MOSFETs

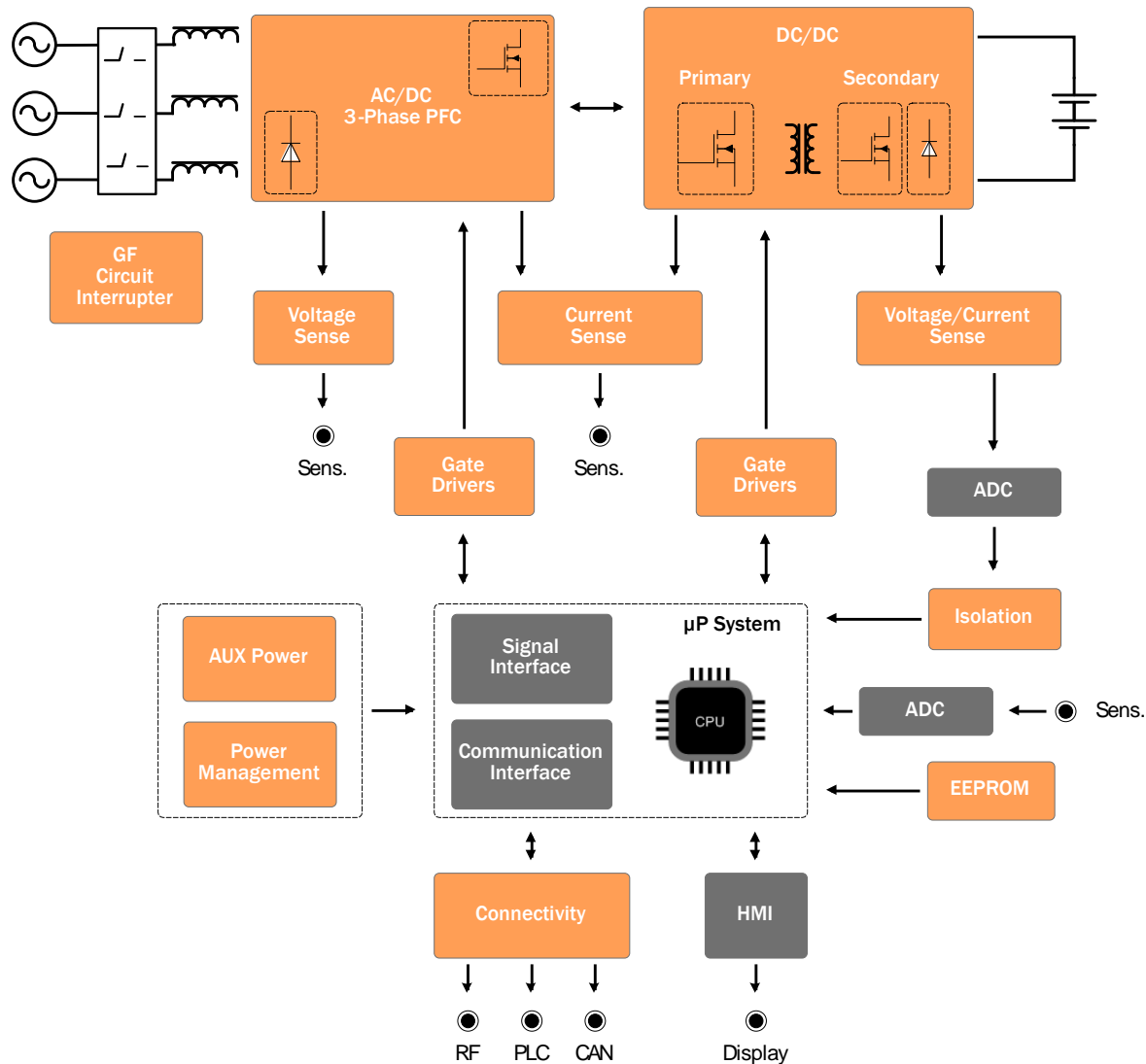




# 25kW building Block

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# FAST EV CHARGING – BLOCK DIAGRAM

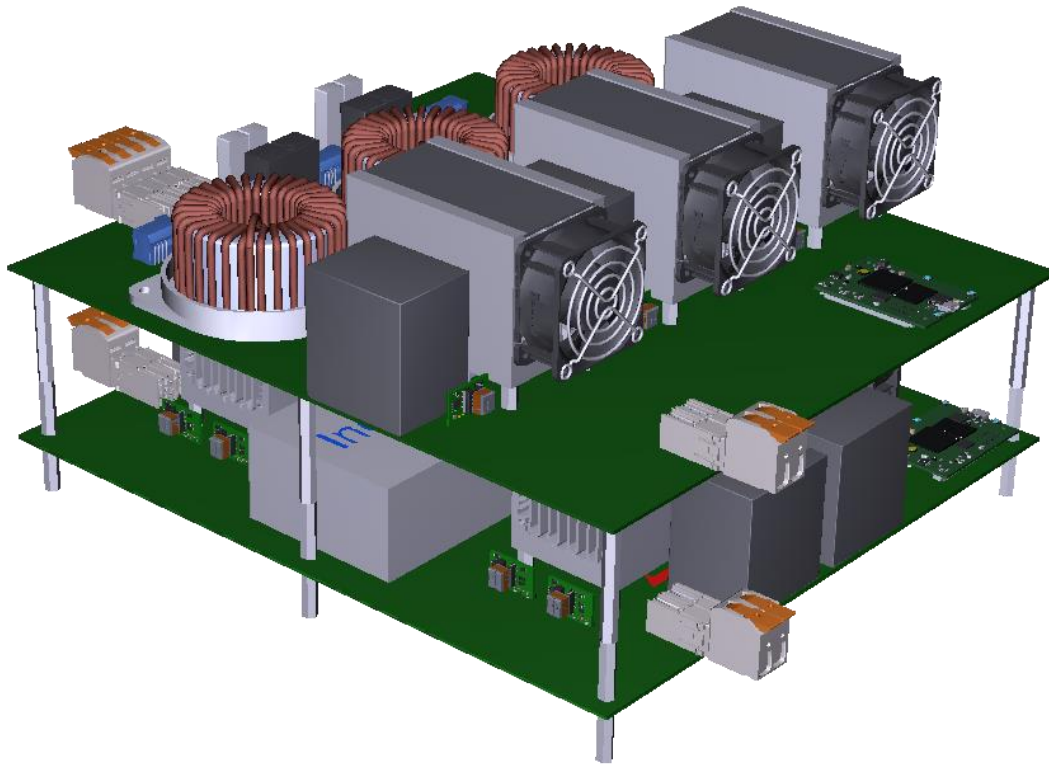


- Active Frontend (PFC)
- Resonant Full Bridge Stage
- Output Rectification
- Voltage Sense
- Current Sense
- LEM Sensor Interface
- AC-DC Regulator/Controller
- DC-DC Regulator/Controller
- CAN Interface
- BLE Interface



# FAST DC CHARGING STRUCTURE

- For DC fast EV charger to deliver power above 100kW :
  - Paralleling is used,
  - Building blocks are typically in the range of 12kW to 75kW...



15-75 kW #1

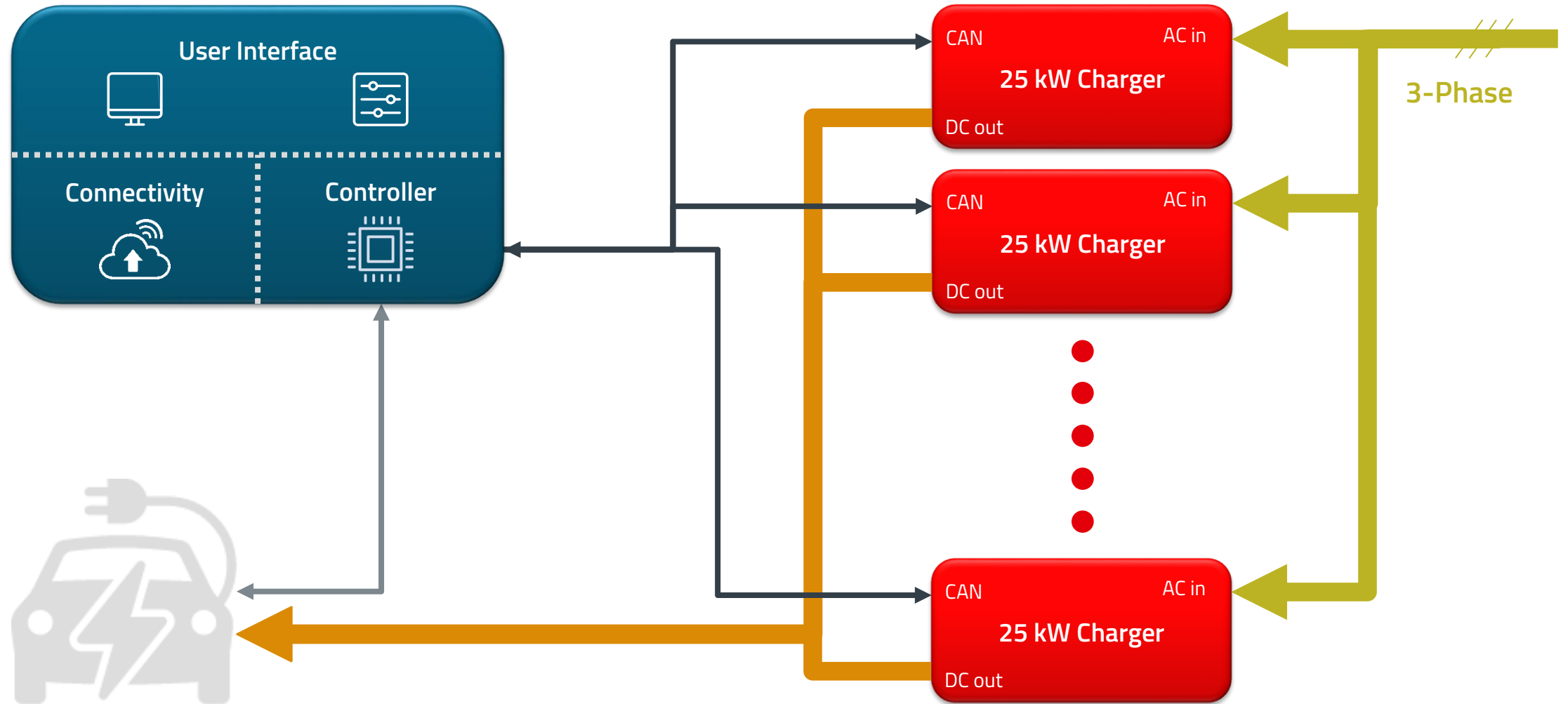
15-75 kW #2

15-75 kW #3

15-75 kW #4



# CHARGING CABINET SOLUTION EXAMPLE

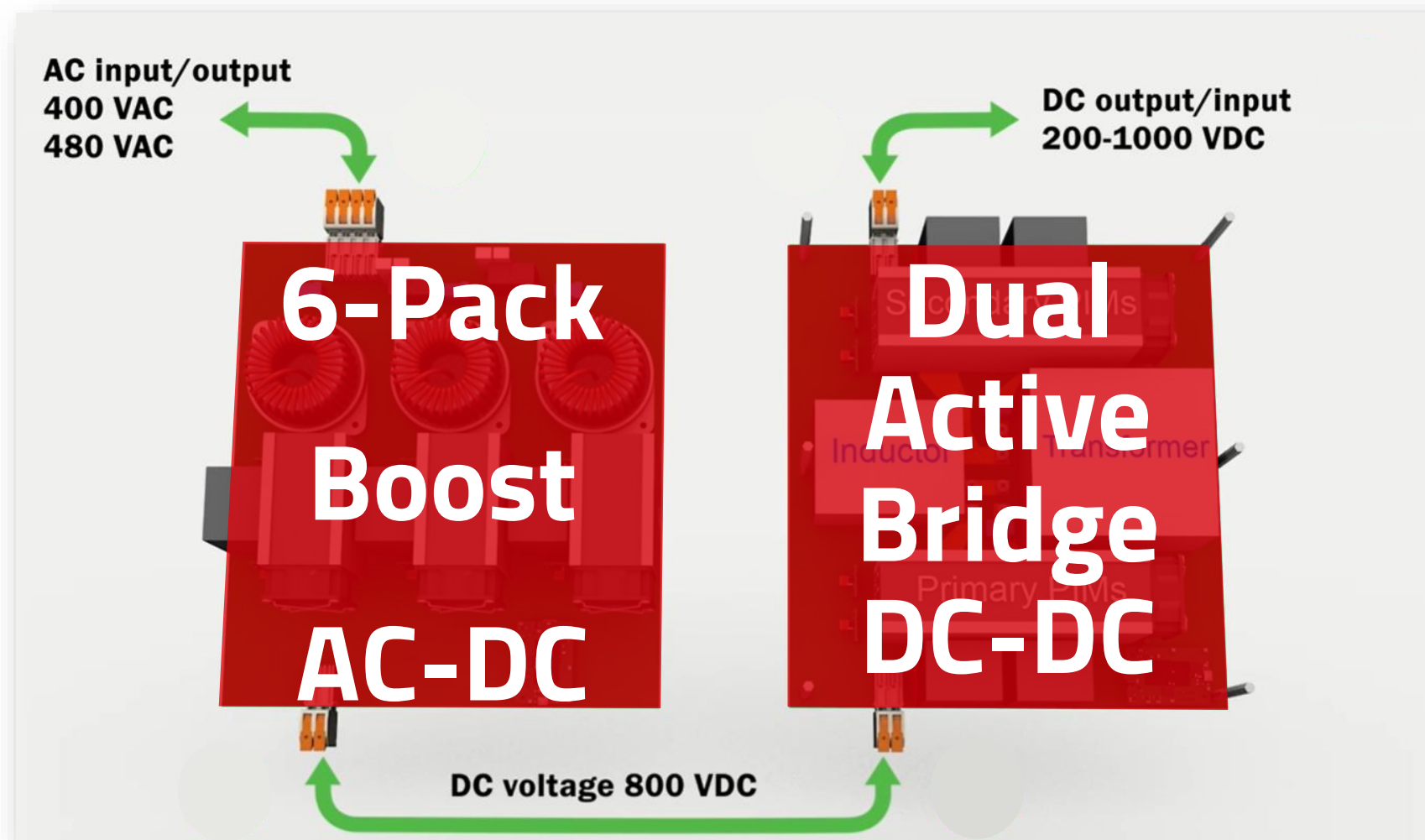


# COMPLETE CHARGER (PFC + DC-DC CONVERTER) SPECIFICATION

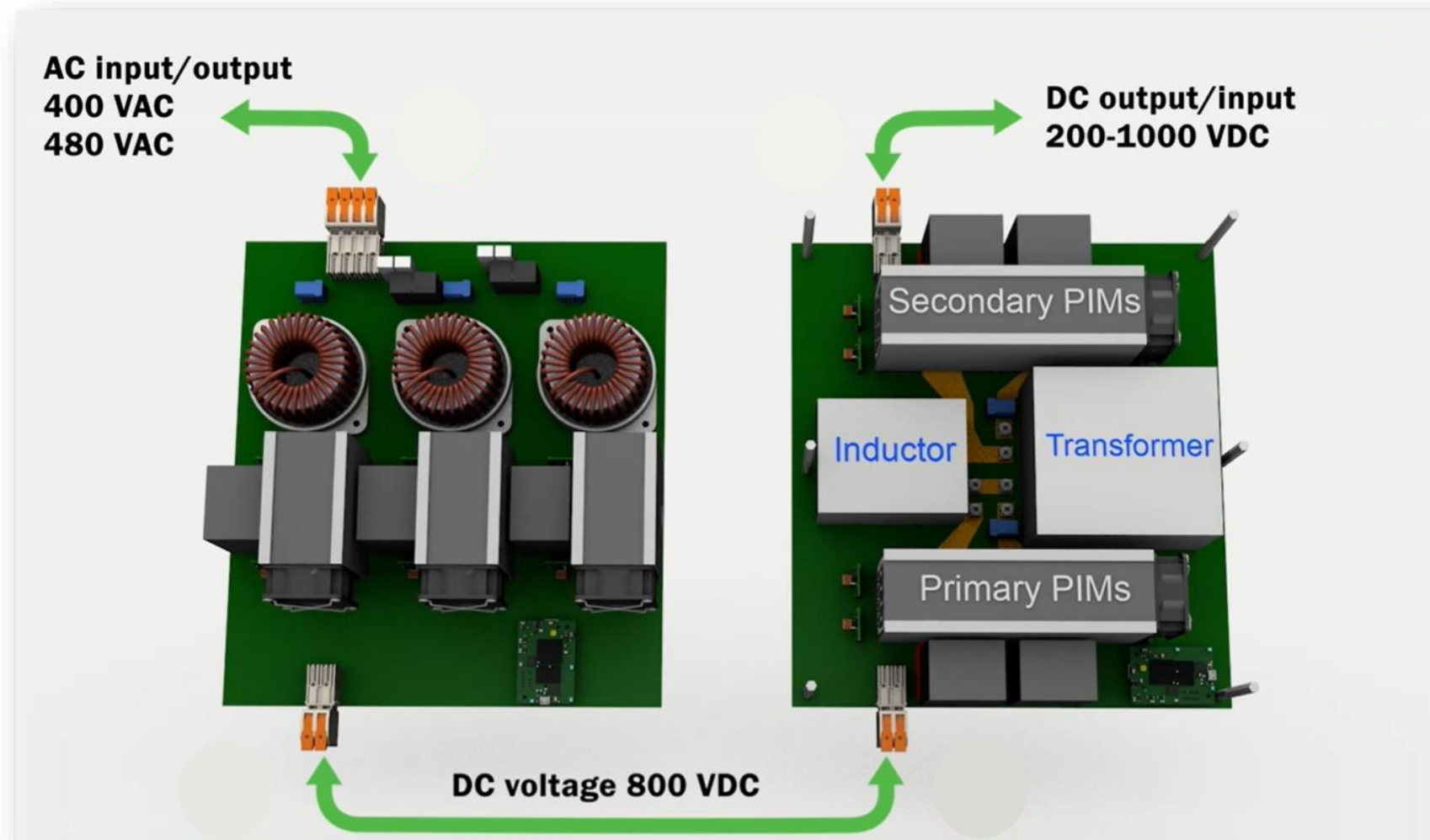
AC input	Voltage input rating	Three-phase 400 Vac (EU), 480 Vac (US)
	Max. input current	40 A
	Frequency	50/60 Hz
	Power factor	>0.99
	Efficiency	>96%
DC output	Output voltage	200 V to 1000 V
	Max. output power	25 kW
	Max. output current	50 A
Protections	Output	OVP, OCP, SC
	Input	UVP, OVP, inrush current
	Internal	Desat (gate driver), thermal (NTC on power device)
User Interface	Push buttons	Yes
	GUI	Yes.
Communication buses	Internal	SPI, I <sup>2</sup> C
	External	Isolated CAN, USB, UART
Environmental	Operating temperature	0°C to 40°C
	Operating mode	Fully <b>Bidirectional</b>
Max. dimensions	PCB	450 x 300 x 280 mm (PFC and dc-dc stacked)
Standards	Regulation	Following guidelines described in EN55011 Class A <b>Will not be tested</b>
	EV systems	Following guidelines described in IEC 61851 <b>Will not be tested</b>



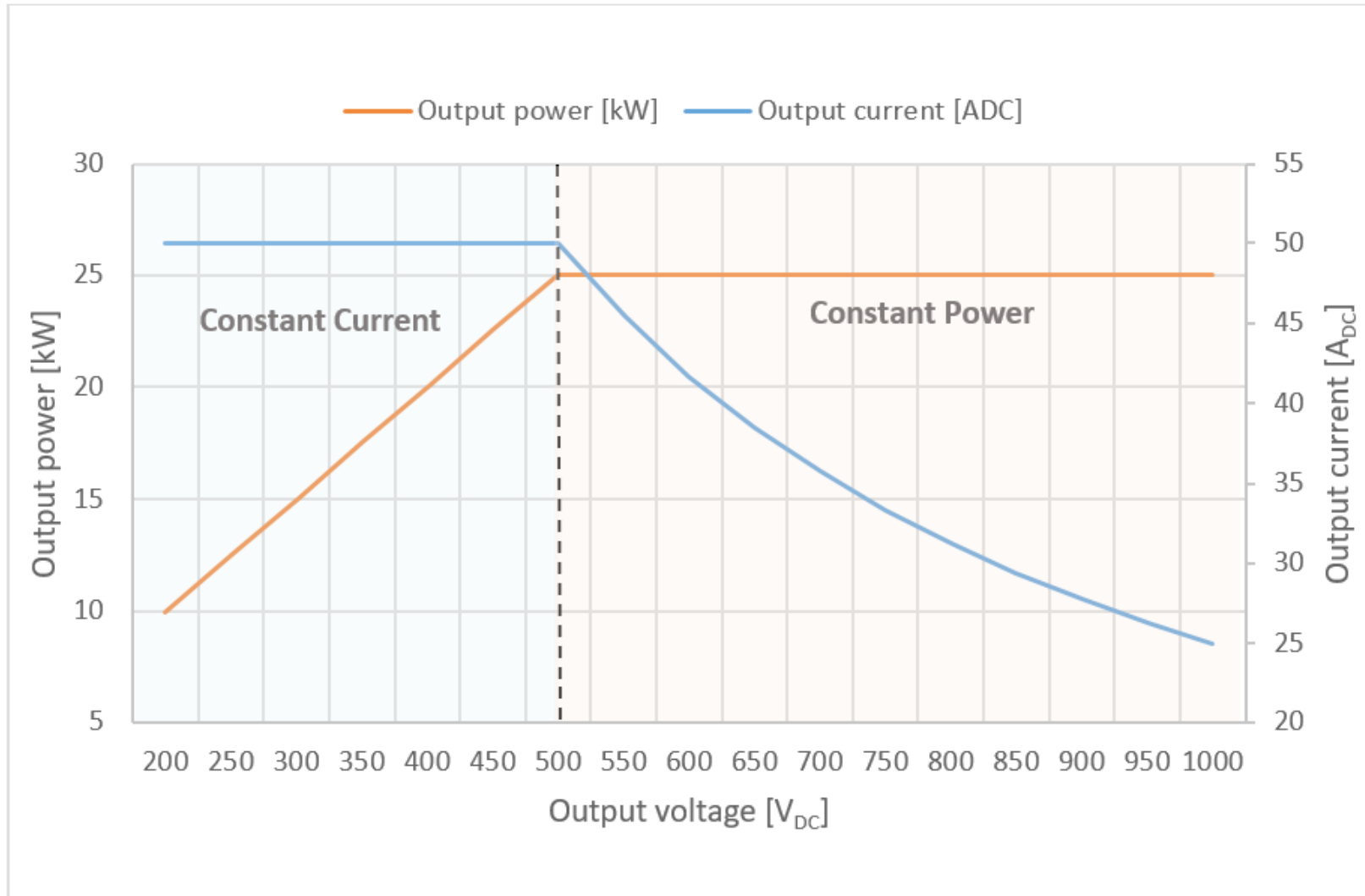
## SYSTEM BOARDS : PFC + DC-DC MECHANICAL SKETCH



## SYSTEM BOARDS : PFC + DC-DC MECHANICAL SKETCH



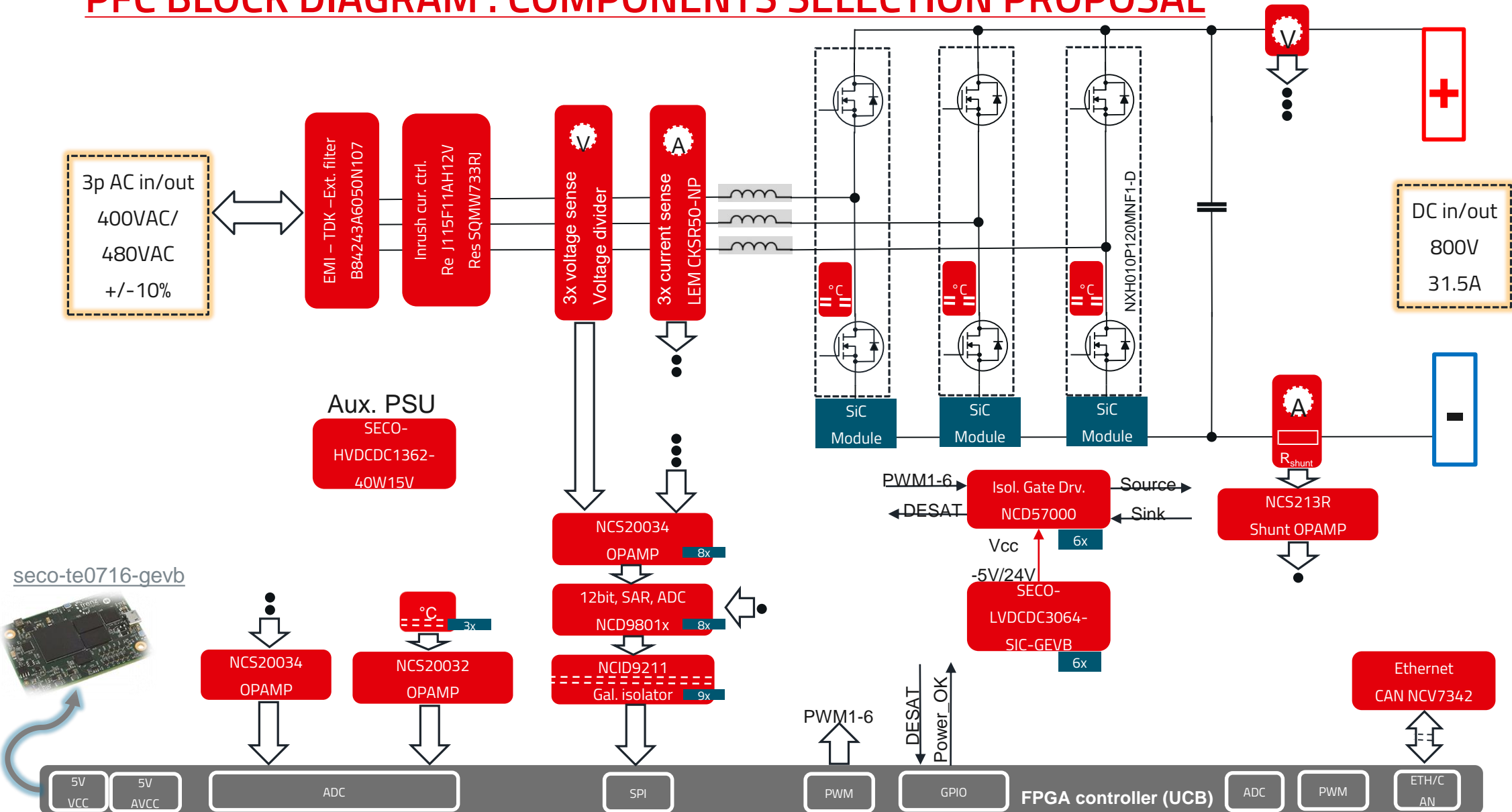
# OUTPUT CHARACTERISTICS



# Products available in onsemi portfolio

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# PFC BLOCK DIAGRAM : COMPONENTS SELECTION PROPOSAL

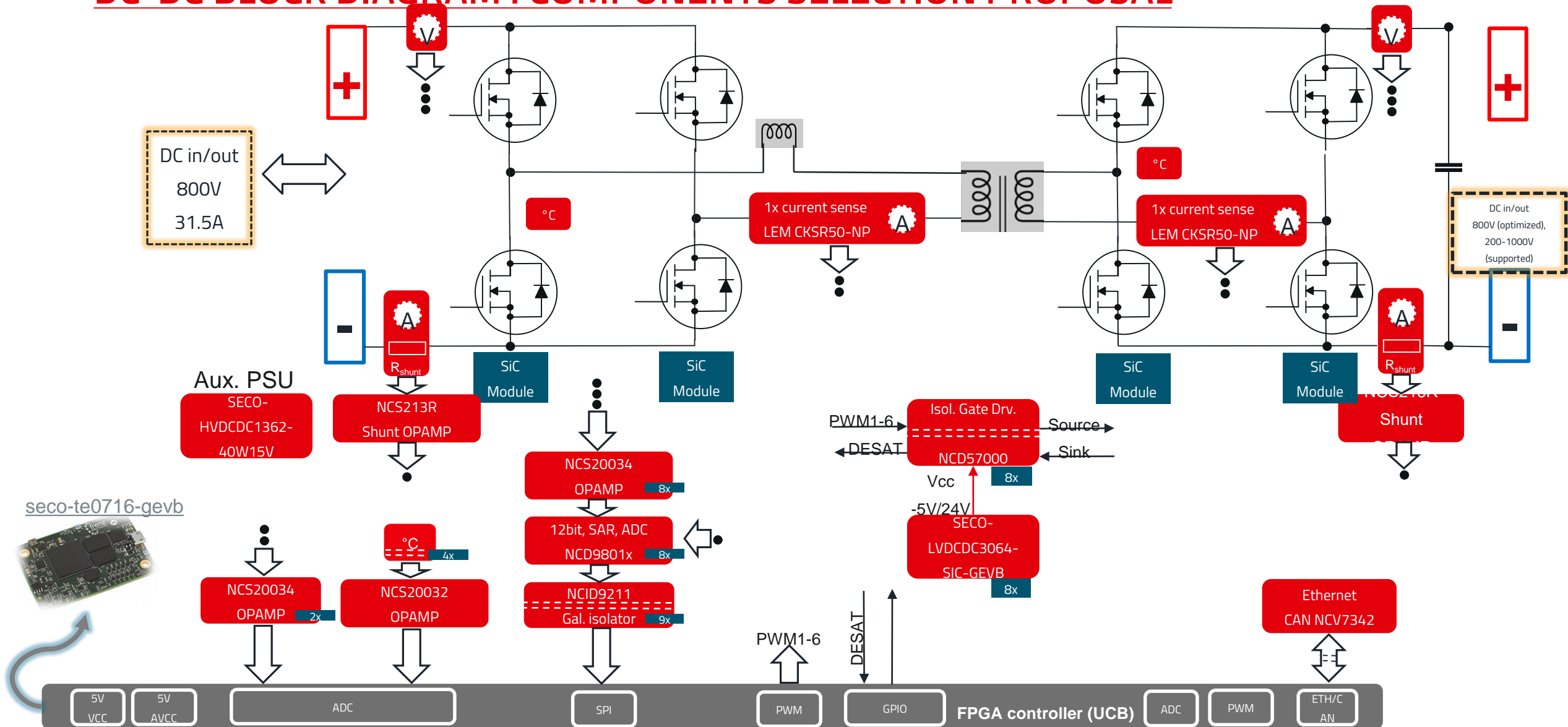




## BILL OF MATERIAL

Function	Part Number
Power Module	NXH010P120MNF1 X3
SiC Gate Driver	NCD57000 X6
Voltage Amplifier	NCS20034
Current Amplifier	NCS213R
General Purpose Amplifier	NCS20032 NCS20034
Digital Isolator	NCID9211
SAR ADC	NCD9801x
Ethernet - CAN	NCV7342
Aux HV PSU	SECO-HVDCDC1362-40W15V with NCP1362
Aux LV PSU	SECO-LVDCDC3064-SIC-GEVB with NCV3064MNTXG

# DC-DC BLOCK DIAGRAM : COMPONENTS SELECTION PROPOSAL



## BILL OF MATERIAL

Function	Part Number
Power Module	NXH010P120MNF1 X4
SiC Gate Driver	NCD57000 X8
Voltage Amplifier	NCS20034
Current Amplifier	NCS213R
General Purpose Amplifier	NCS20032 NCS20034
Digital Isolator	NCID9211
SAR ADC	NCD9801x
Ethernet - CAN	NCV7342
Aux HV PSU	SECO-HVDCDC1362-40W15V with NCP1362
Aux LV PSU	SECO-LVDCDC3064-SIC-GEVB with NCV3064MNTXG

# Modules

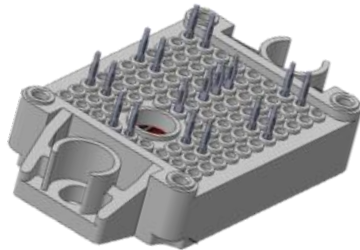
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For high power applications' scaling

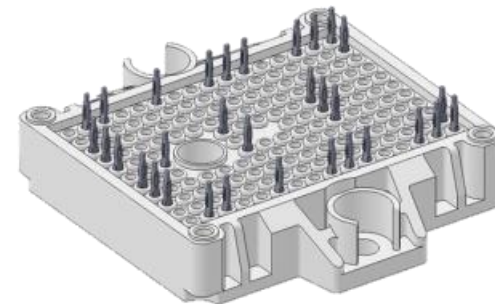
# POWER SCALING VS MODULE FOR HALF-BRIDGE MODULES

Output Power	Part number	Description
~ 6 kW	NXH040P120MNF1	Half Bridge 2-PACK 1200V 40mohm SiC MOSFET
~ 12 kW	NXH020P120MNF1	Half Bridge 2-PACK 1200V 20mohm SiC MOSFET
~ 25 kW	NXH010P120MNF1	Half Bridge 2-PACK 1200V 10mohm SiC MOSFET
~ 50 kW	NXH006P120MNF2	Half Bridge 2-PACK 1200V 6mohm SiC MOSFET

F1



F2



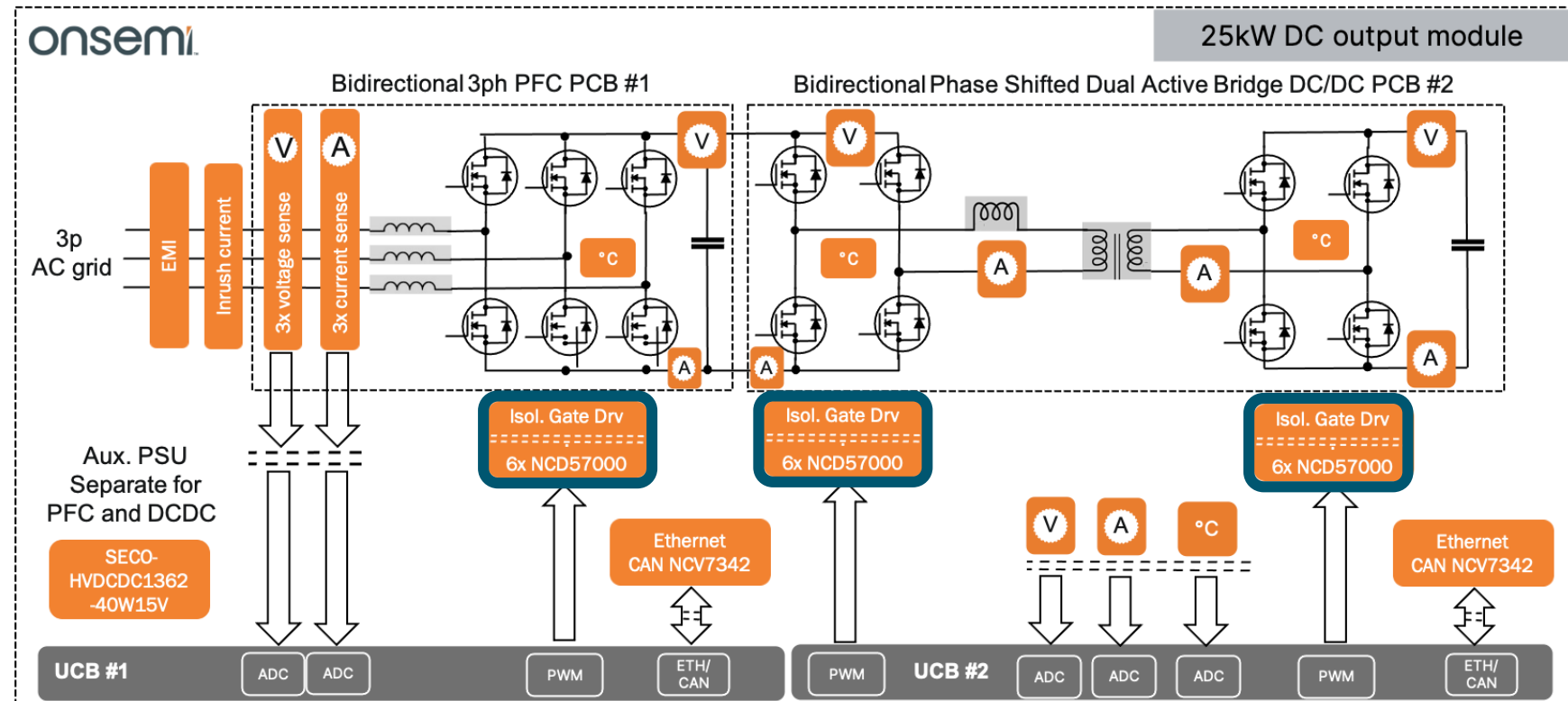


# Gate drivers

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# DRIVERS SELECTION FOR THE 25KW POWER STAGE

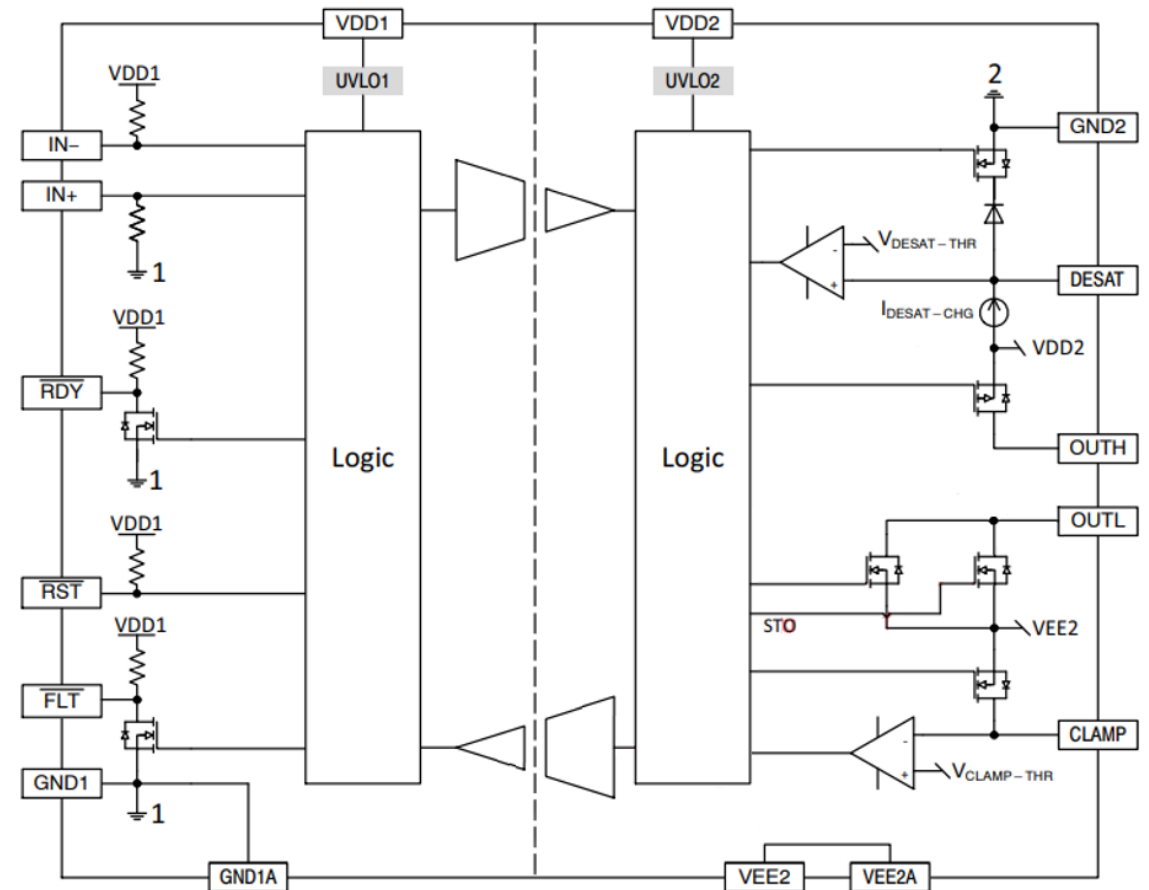
- The NCD57000 was selected because it offers the following features :
  - 50 ns Propagation delay and 10 ns delay mismatch,
  - Low output internal impedance
  - +4 A / -6 A capability
  - 25-V output range
  - 100-V/ns Immunity
  - Active Miller Clamp
  - DESAT protection
  - 5-kVrms isolation
  - 8-mm creepage



# INTRODUCING NCD(V)57100 / 101

## ■ Highlights

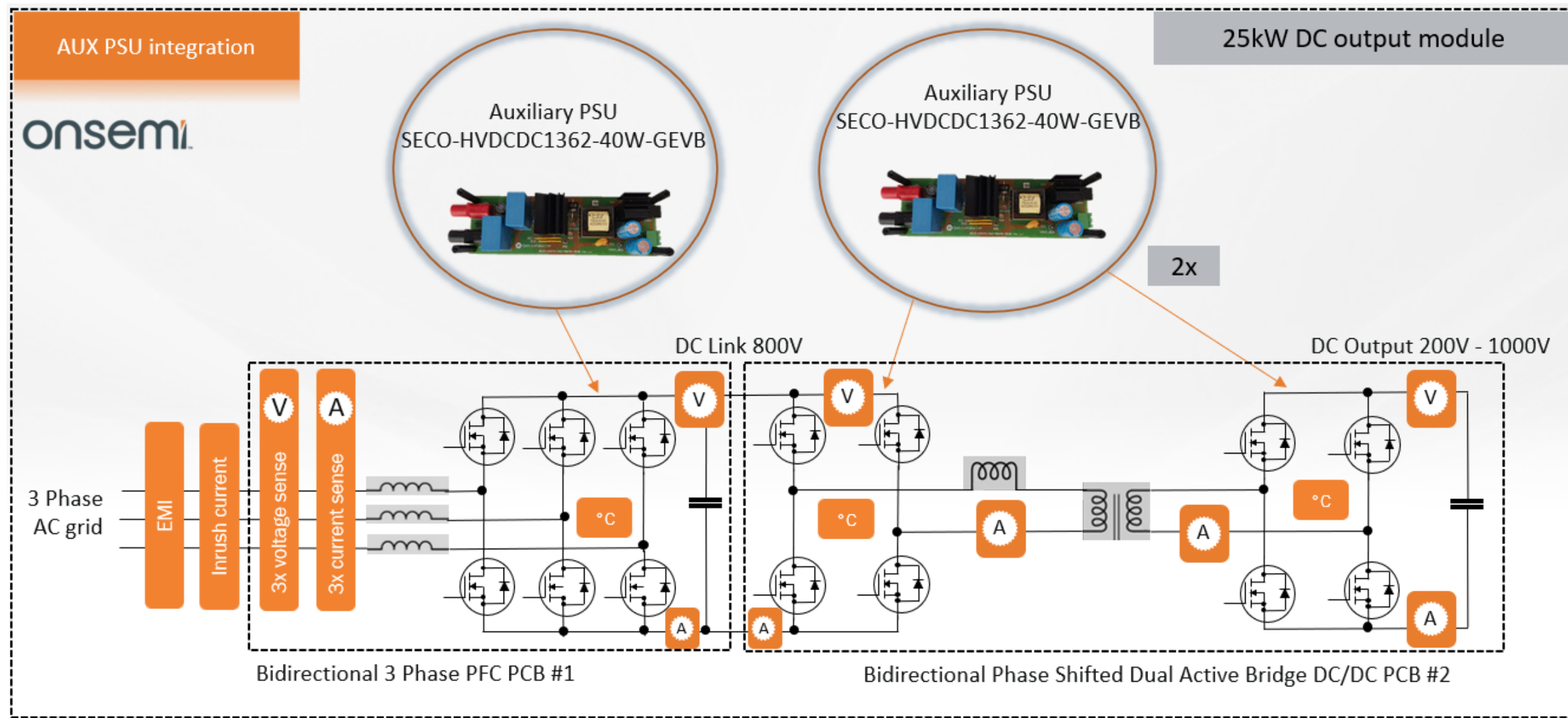
- Pin2Pin Drop-In Replacement to NCD(V)57000/001
- Addresses all known issues in NCD(V)57000/001
- Identified root cause, fixed & verified all issues
- VDD2-VEE2 (VMAX2) increased from 25 V to 32 V
- Improved RSTb Function
- New DESAT Diagnostics Test (Patent Pending)
- Rev A Samples Available (Require Errata)
- Rev B Samples Available Q2/End
- Production Q3'2022
- NCD(V)57000 will not be EOL'd



# Auxiliary Supply sockets

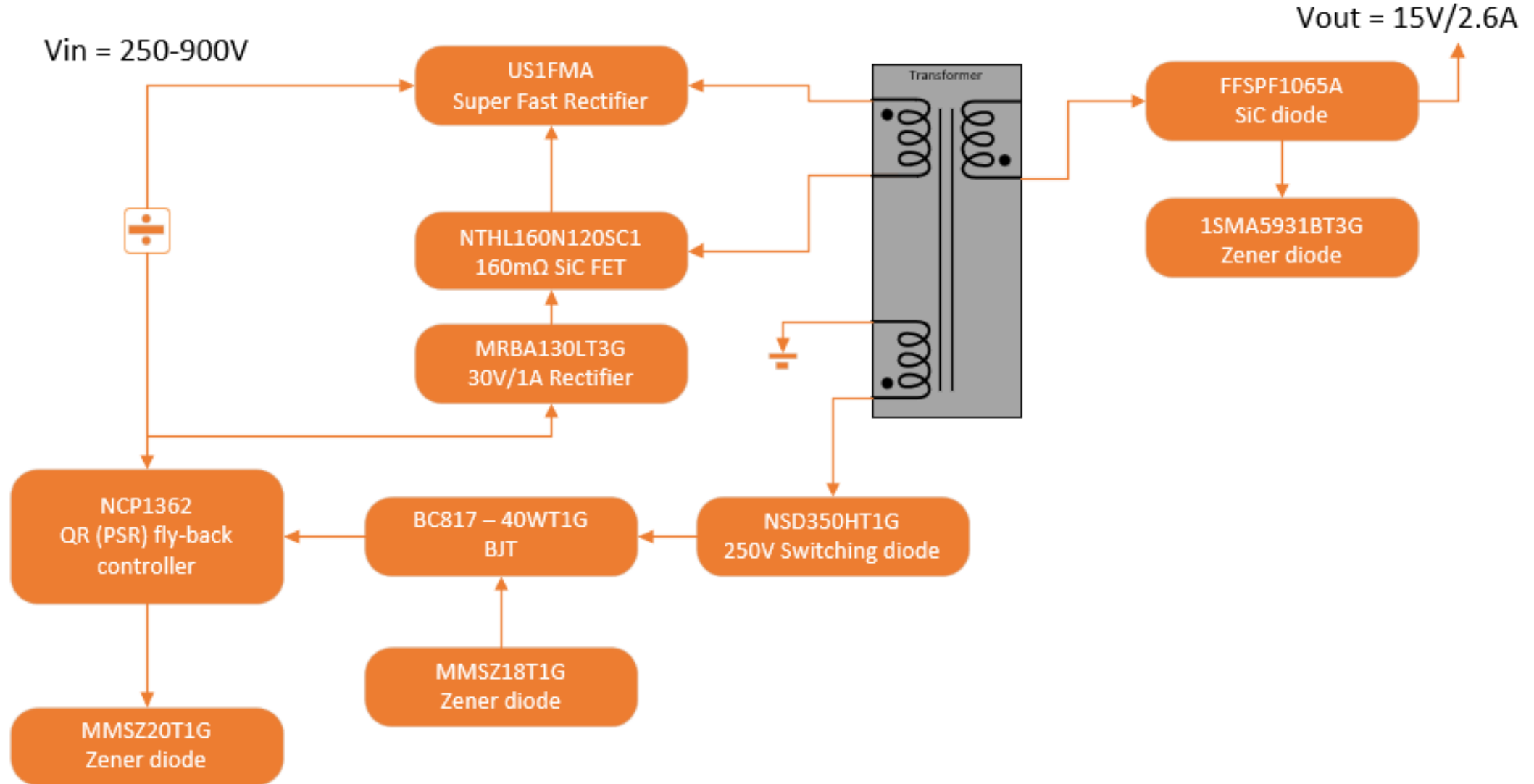
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## AUXILIARY SUPPLIES NEED





# SECO-HVDCDC1362-40W-GEVB BLOCK DIAGRAM



# AUXILIARY SUPPLY DESIGN : SECO-HVDCDC1362-40W-GEVB

- Topology : **40 W - 15 V / 2.6 A** Flyback boundary conduction mode + ZCD clamp
  - PWM : NCP1362 driving SiC MOSFET with 0 V - 12 V gate drive
    - (no external dedicated SiC MOSFET driver helps saving cost)
  - Main Switch : 1200 V, 160 mW NTHL160N120SC1 SiC MOSFET
    - We keep 100 V headroom for the SiC MOSFET.
    - For more headroom : 1700 V, 1 W SiC MOSFET
  - ZCD clamp : US1FM1 Super Fast diode / 160V TVS
  - Secondary rectifier diode : FFSP0665B
    - Due to large input swing

# Amplifier (Voltage and Current)

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# EV CHARGING STATIONS – SENSING CIRCUITS

## Voltage Sensing

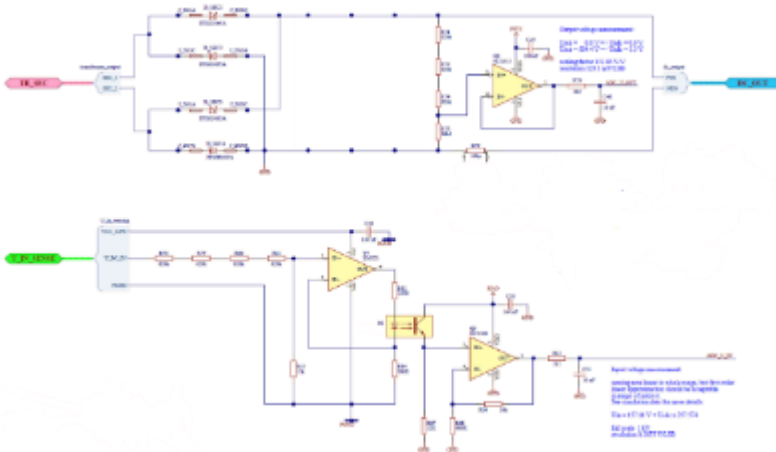
Medium signal bandwidth

High accuracy needed

Solution based on **NCS333/2333/4333**

Output Voltage Sensing

Input Voltage Sensing



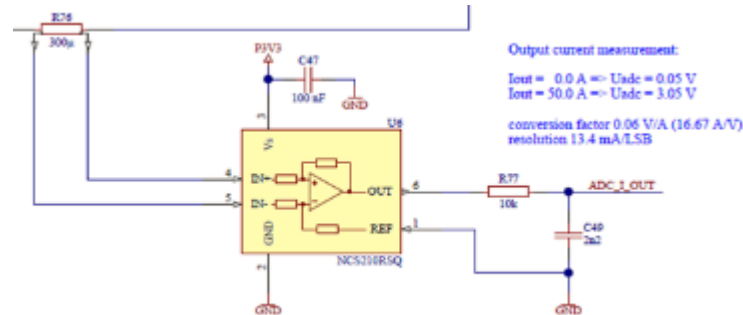
## Current Sensing with Resistor

High signal bandwidth

High speed needed

Solution based on **NCS210RSQ**

LLC Output Current Sensing



## Current Sensing with LEM Sensor

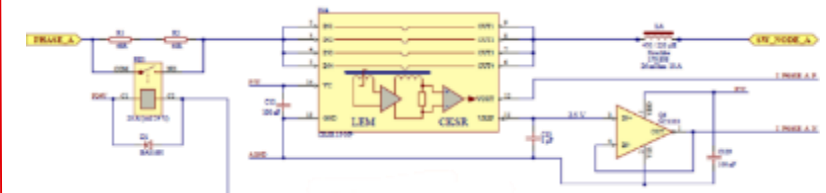
High signal bandwidth

High speed needed

Solution based on **NCS333**

Interface to LEM sensor

used for inrush current detection



**onsemi** Advantages: Verified function and layout in lab evaluation board

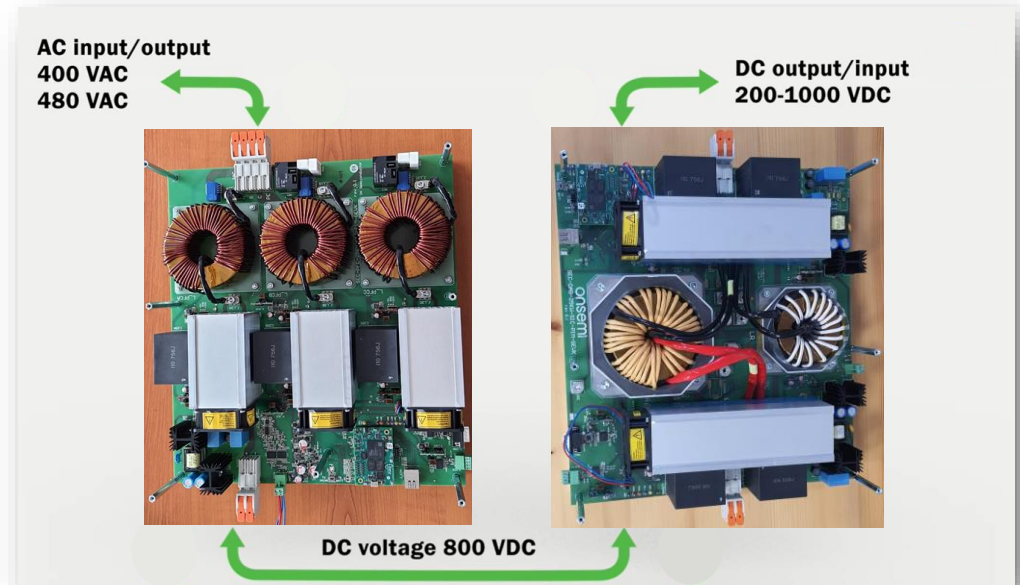
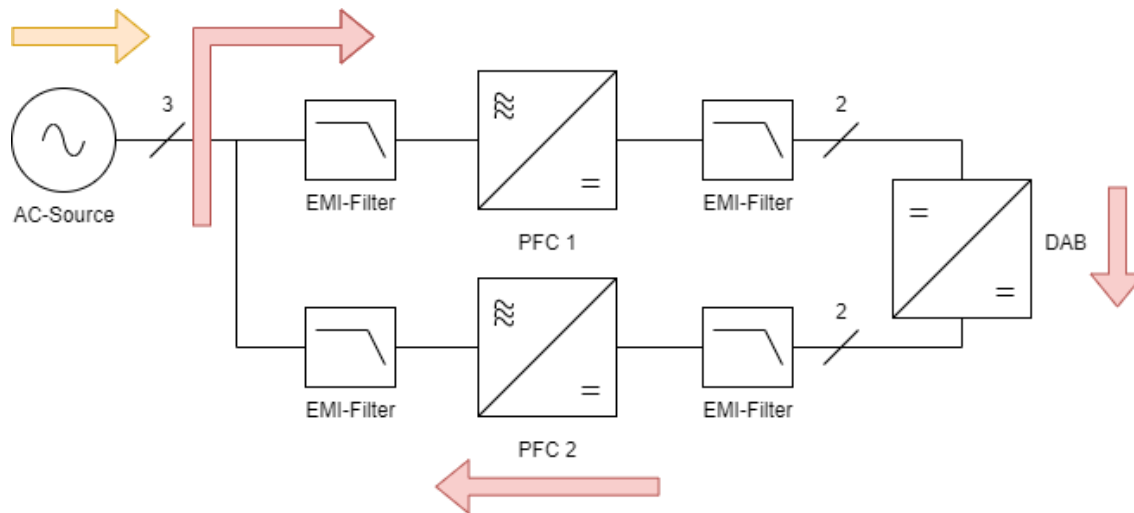
# Measurement and Results

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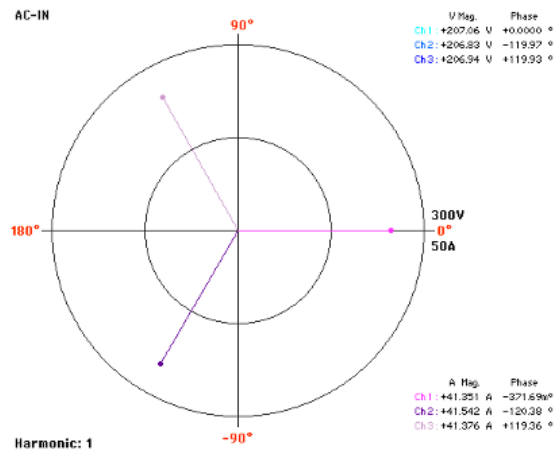
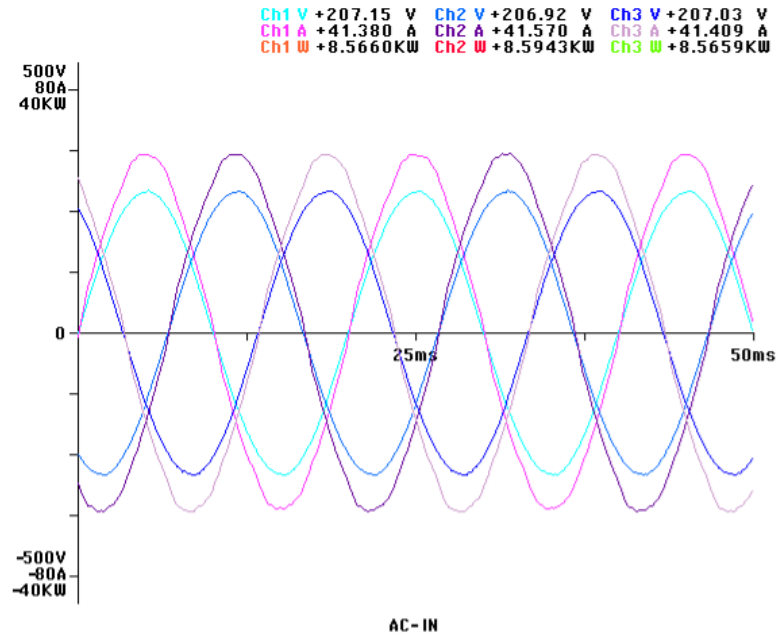
# MEASUREMENT – BLOCK DIAGRAM



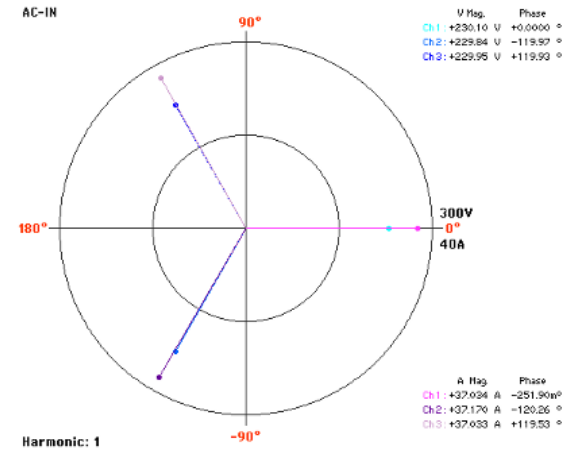
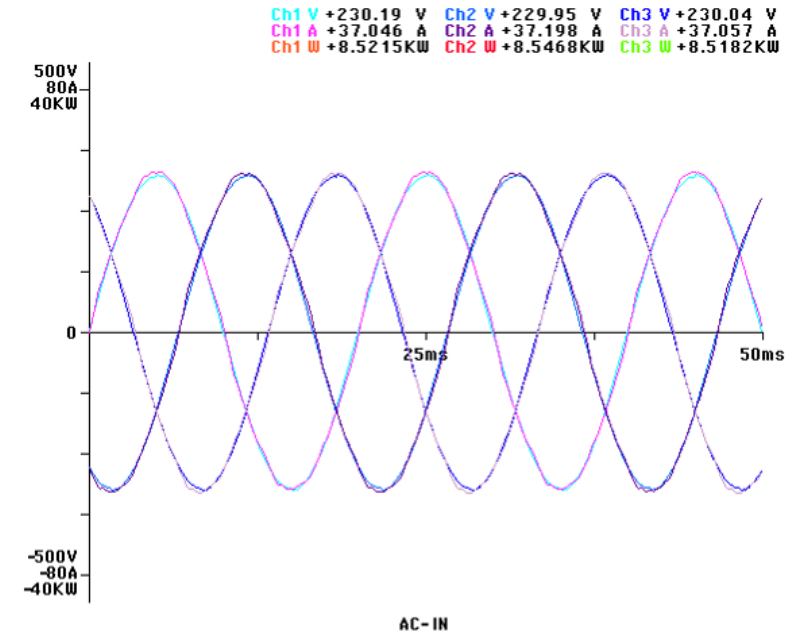
- To reduce power consumption, we use the bidirectional operation to load a first stage with a second stage operating reverse and re-inject the first stage output power into the grid.



# INPUT VOLTAGE AND CURRENT



Low line  
207VAC

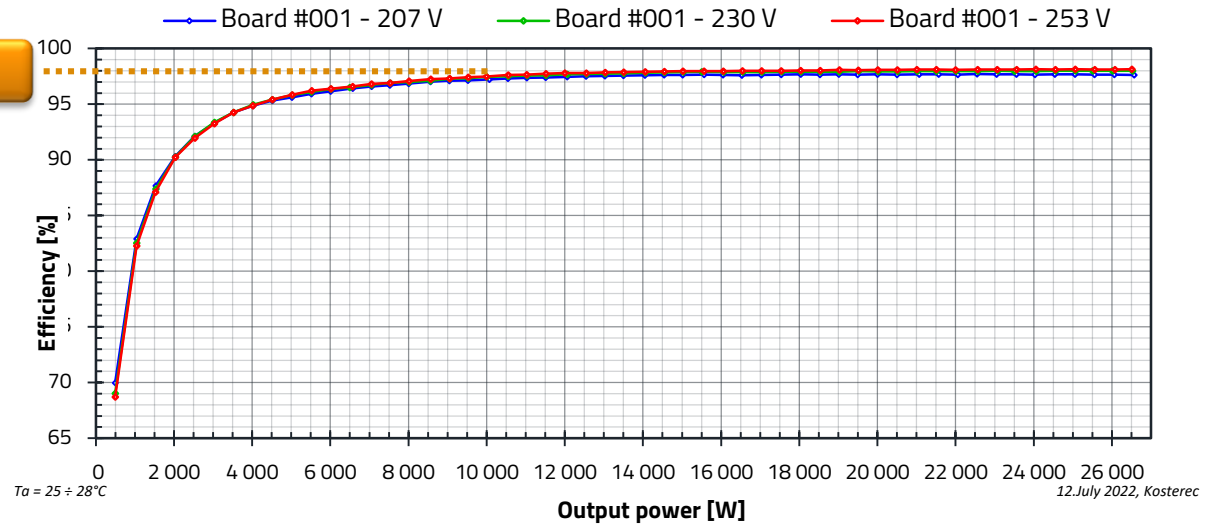


Nominal line  
230VAC

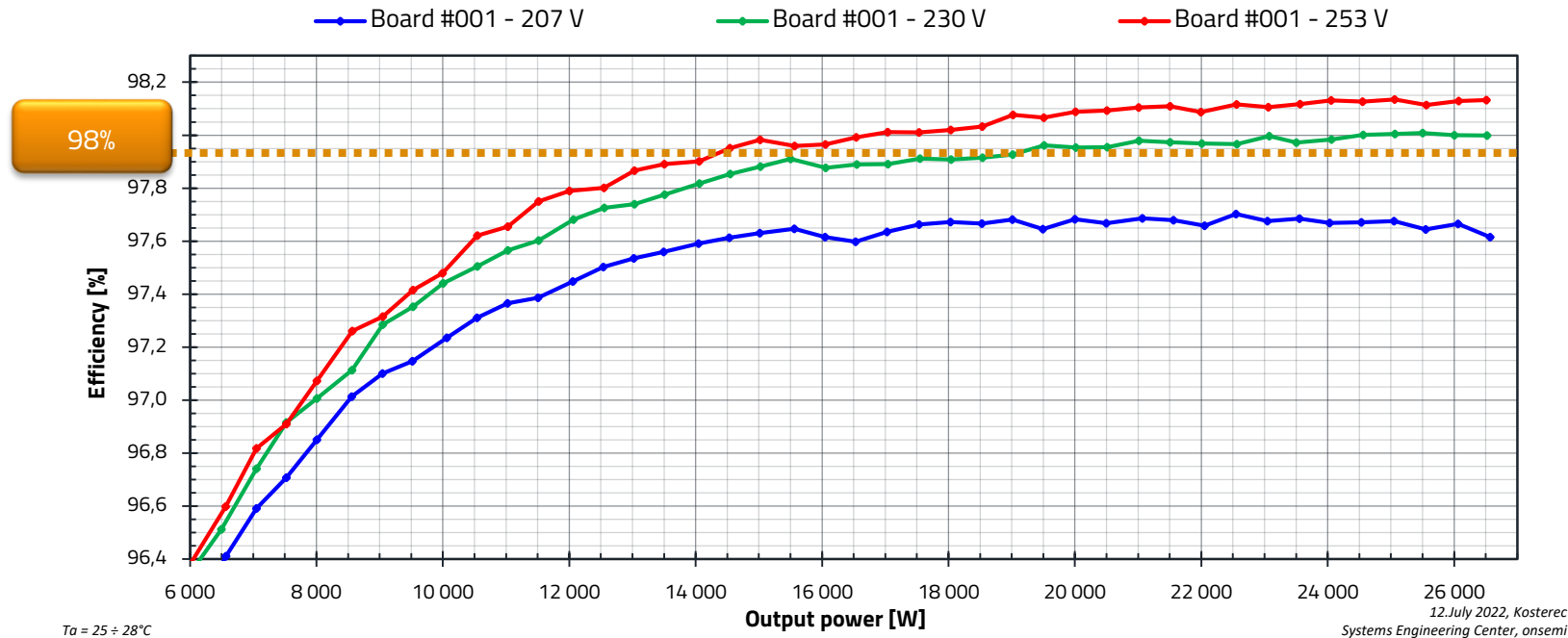


# ACTIVE FRONT END - EFFICIENCY

98%



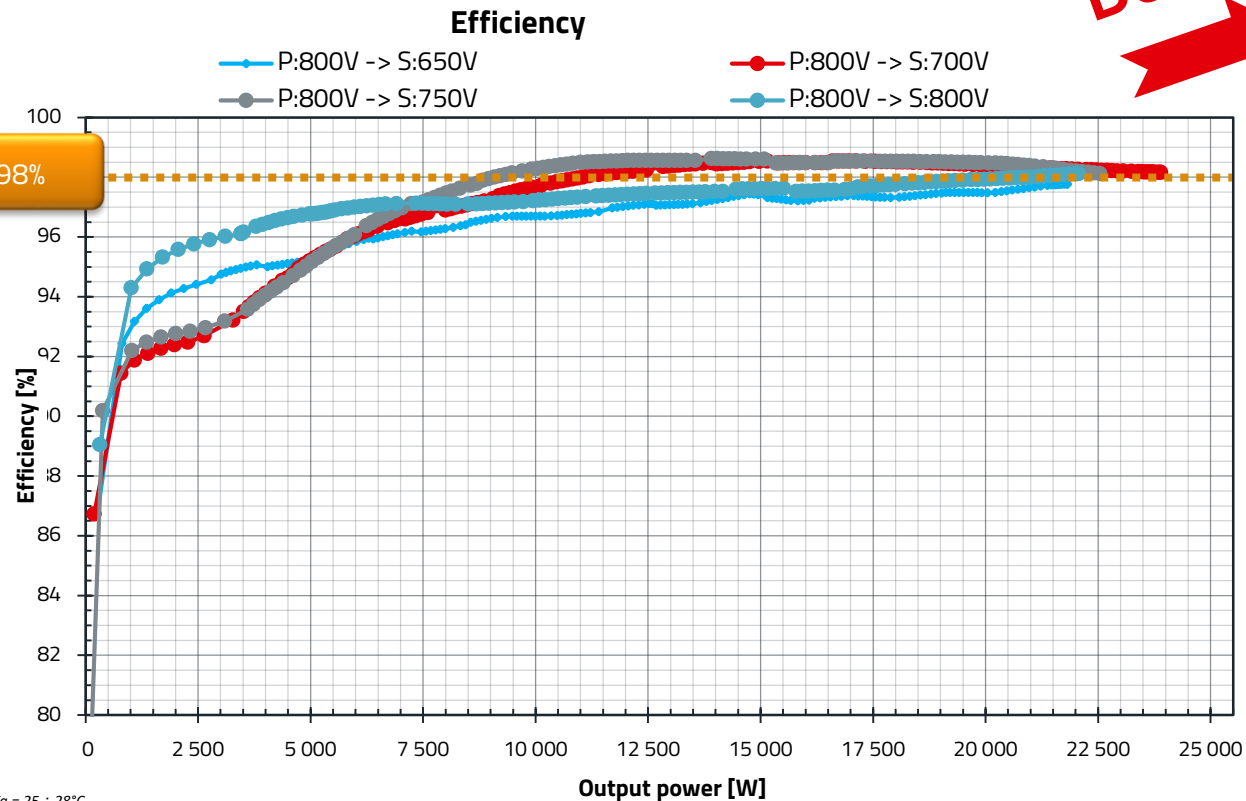
Detail from 6-26.5kW



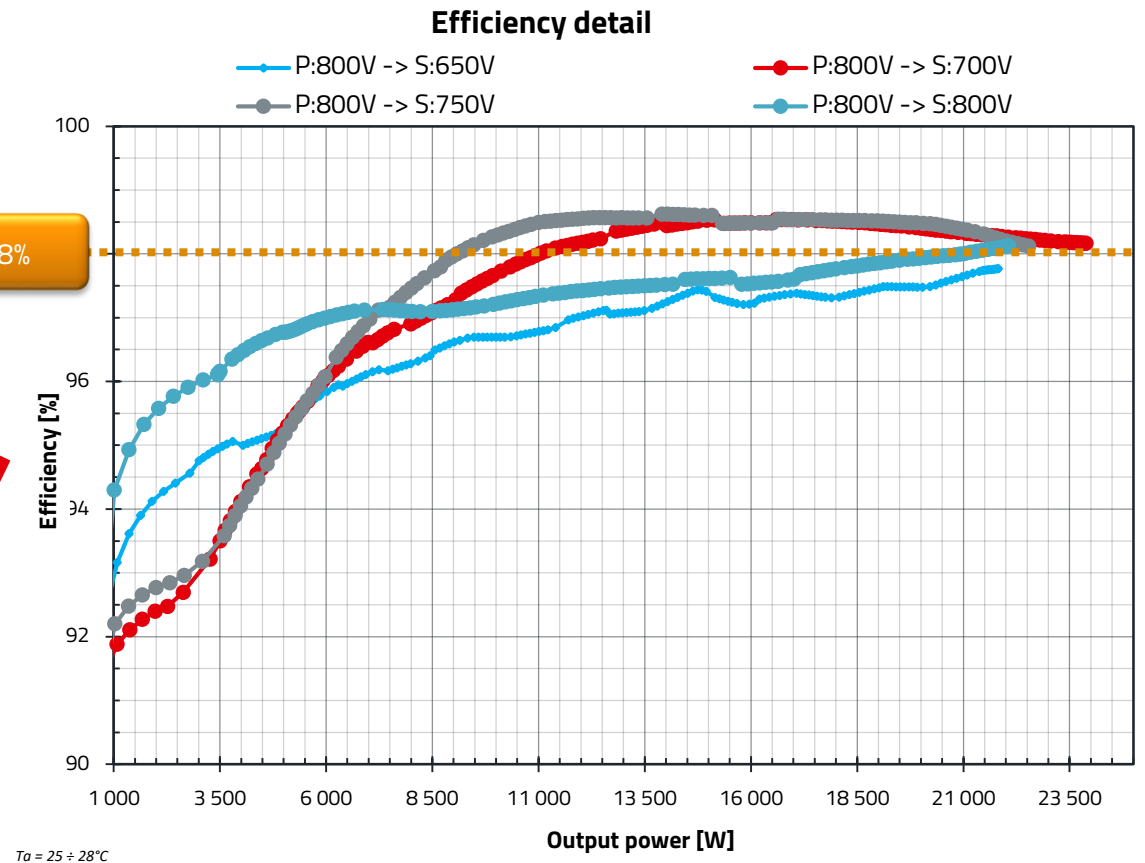
25kW power range

Note: Efficiency is with included losses in input and output EMI filter

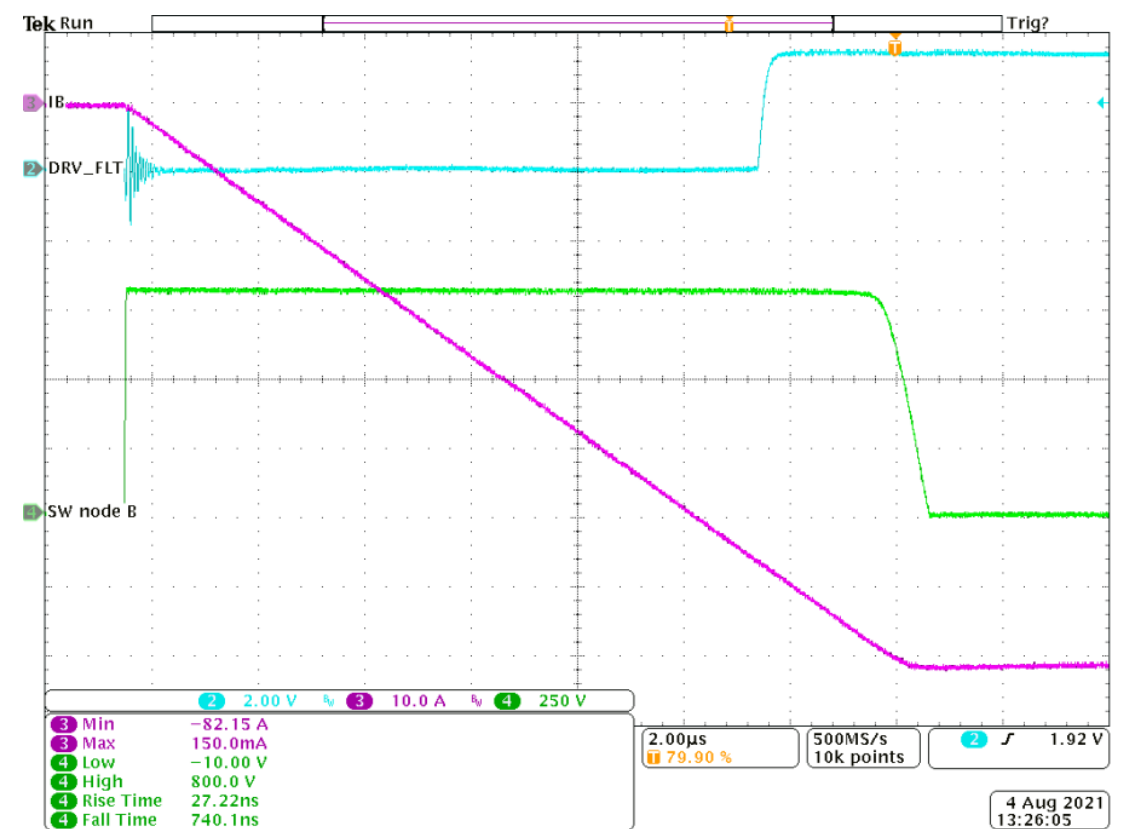
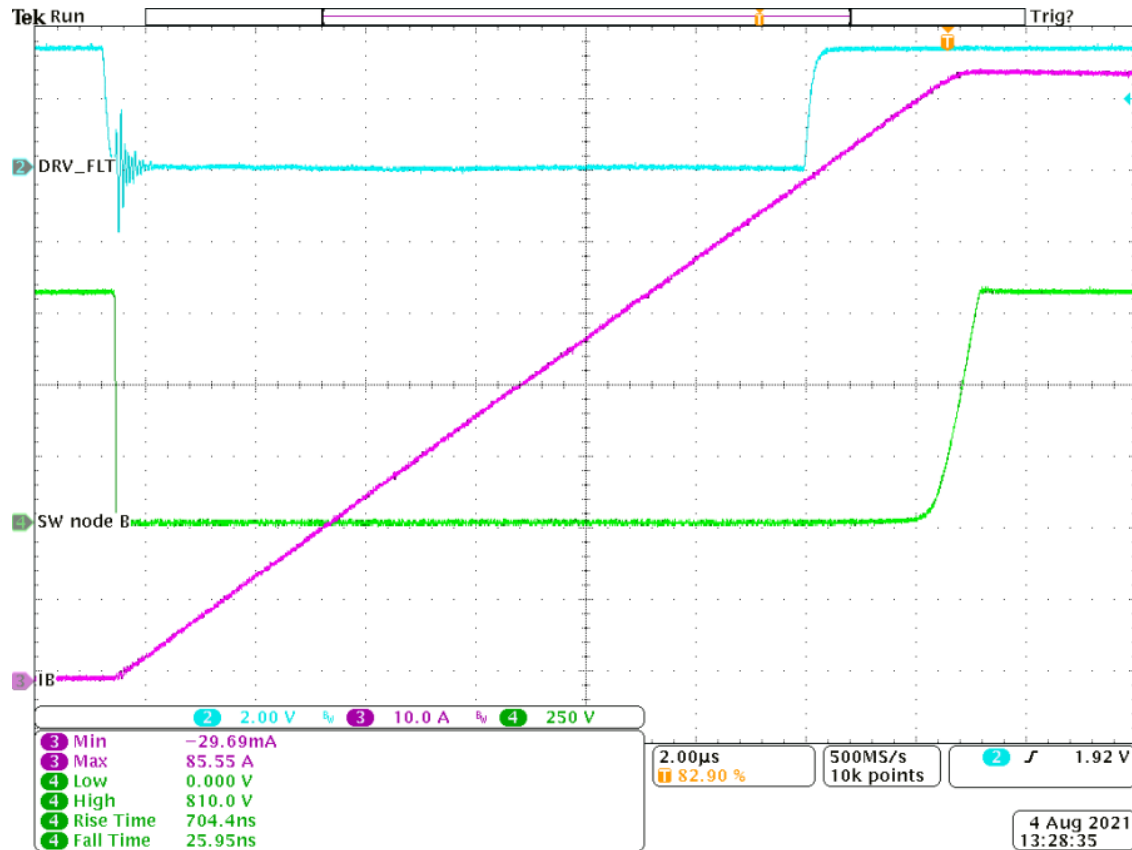
# DUAL ACTIVE BRIDGE EFFICIENCY



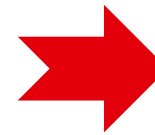
Detail



# DESAT FUNCTION THRESHOLD AND OPERATION



Theoretical calculated DESAT threshold current : 85A to 115A  
Measurement on several samples resulted to range : 68A to 118A



✓ DESAT can be used  
to protect SiC MOSFET

# Conclusion

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# CONCLUSION

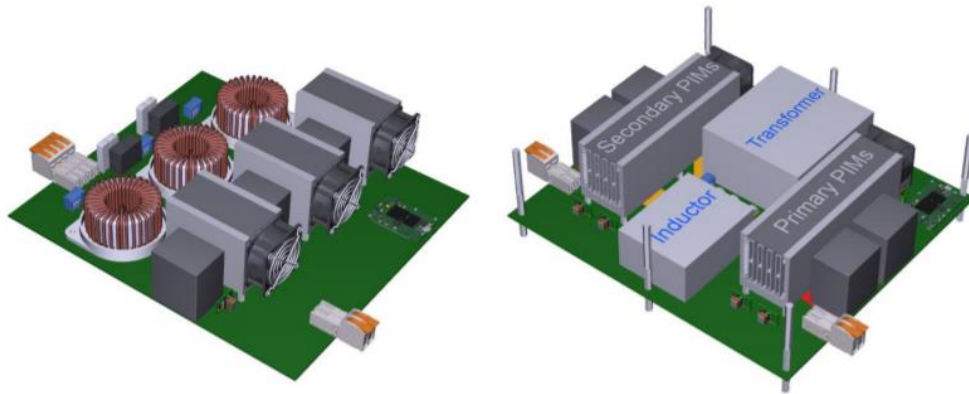
- Various high-power topologies can be used for Fast EV Charger
- For that power level, Modules is the best way to go
- More than 10 product families can be addressed with **onsemi** portfolio
  - Modules,
  - Gate drivers,
  - Operational Amplifiers and Current Sensing Amplifiers,
  - Isolators,
  - Auxiliary Supplies,
  - Communication interface, ...

# ONSEMI EV CHARGING STATION

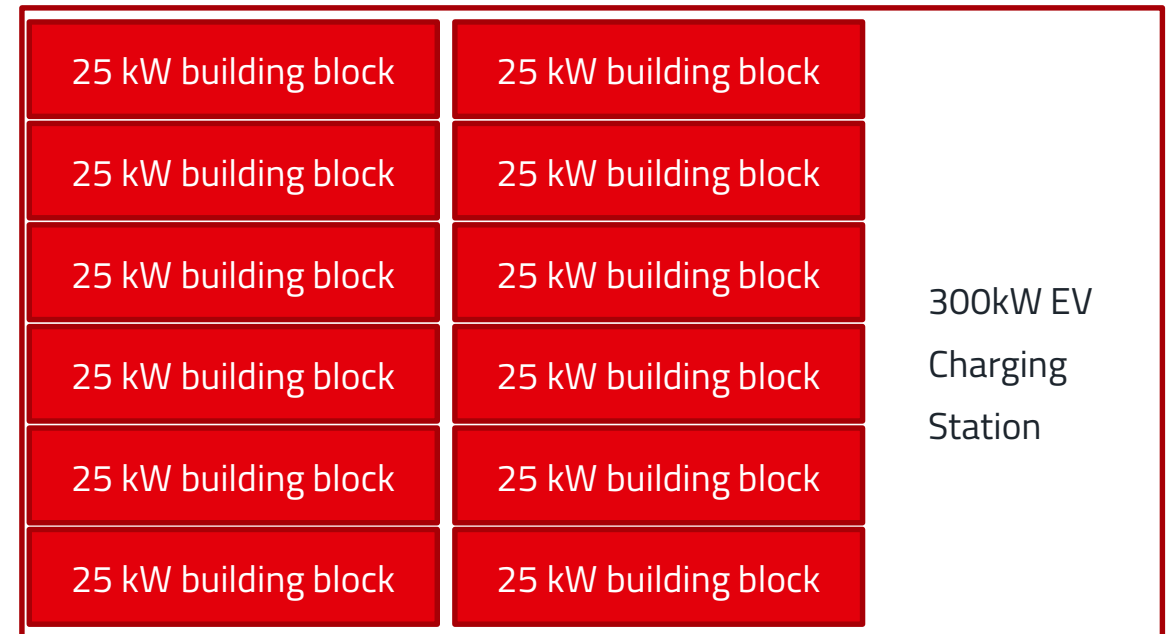
## 25kW building block solution support

Developing A 25-kW SiC-Based Fast DC Landing page :

<https://www.onsemi.com/design/tools-software/evaluation-board/SEC-25KW-SIC-PIM-GEVK>

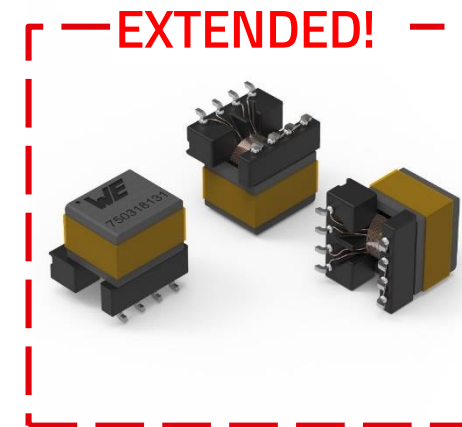
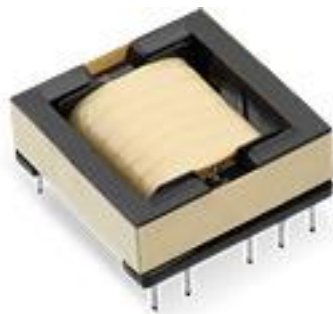


PFC stage and DC-DC stage for **onsemi**  
25kW EV Charging Station Solution



12 x 25kW building blocks  
used in 300kW EV Charging Station

EV Charging landing page : [www.onsemi.com/dc-fast-charging](http://www.onsemi.com/dc-fast-charging)



onsemi™

PFC CHOKE

AUXILIARY GATE DRIVE TRANSFORMER

SPECIFICATION AND APPLICATION

Stroe Octavian Tudor  
Product Definition Engineer Eastern Europe

**WÜRTH ELEKTRONIK** MORE THAN YOU EXPECT



# OCTAVIAN-TUDOR STROE

## ■ **Diploma**

- Audio Systems BSc degree, Electronics specialization from University of Huddersfield, UK
- Optical Compression MSc from University of Huddersfield

## ■ **Experience**

- Background in Power and Audio Electronics design and testing
- High Voltage, High Current PoL converters
- PCB Layout and 3D Design
- Product Definition Engineer at Würth Elektronik since 2022
- Responsible for EMC support to IC Houses in Europe





WÜRTH  
ELEKTRONIK  
MORE THAN  
YOU EXPECT

onsemi™

## AGENDA

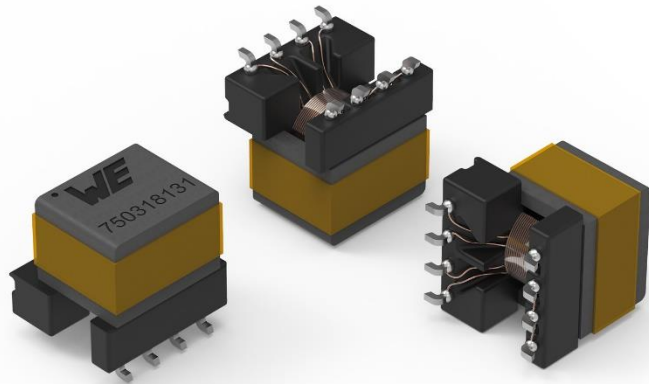
- Extended WE-AGDT Transformers
  - New parts and characteristics
  - Application in onsemi 25kW charger
  - Typical applications and interwinding capacitance
- New WE-TORPFC Overview
  - Product family and characteristics
  - Application in onsemi 25kW charger
  - Specification and measurements
- Why flat wire?
  - Skin and proximity effects
  - Round vs Flat wire measurements
  - Conclusion and equivalent circuit



# WE-AGDT EXTENDED SERIES OVERVIEW

## Auxiliary Gate Drive Transformers

AEC – Q200  
Qualified



- 14x Catalogue parts in stock – No MOQ
  - Up to 6W output power
  - Wide Input voltage: 6-36V
  - Flyback, LLC, Half-Bridge Topologies
  - AEC-Q200 Grade 1
- Characteristics
  - Interwinding capacitance down to <1 pF
  - Tiny surface mount EP7 package
  - Dielectric insulation up to 4 kV AC
  - Basic insulation for 568 Vrms / 800 Vpk
  - Safety: IEC62368-1 / IEC61558-2-16
- Applications
  - Industrial drives
  - AC motor inverters
  - HEV/EV charging station
  - Battery chargers
  - Solar inverters
  - Data centers

## EXTENDED SERIES OVERVIEW

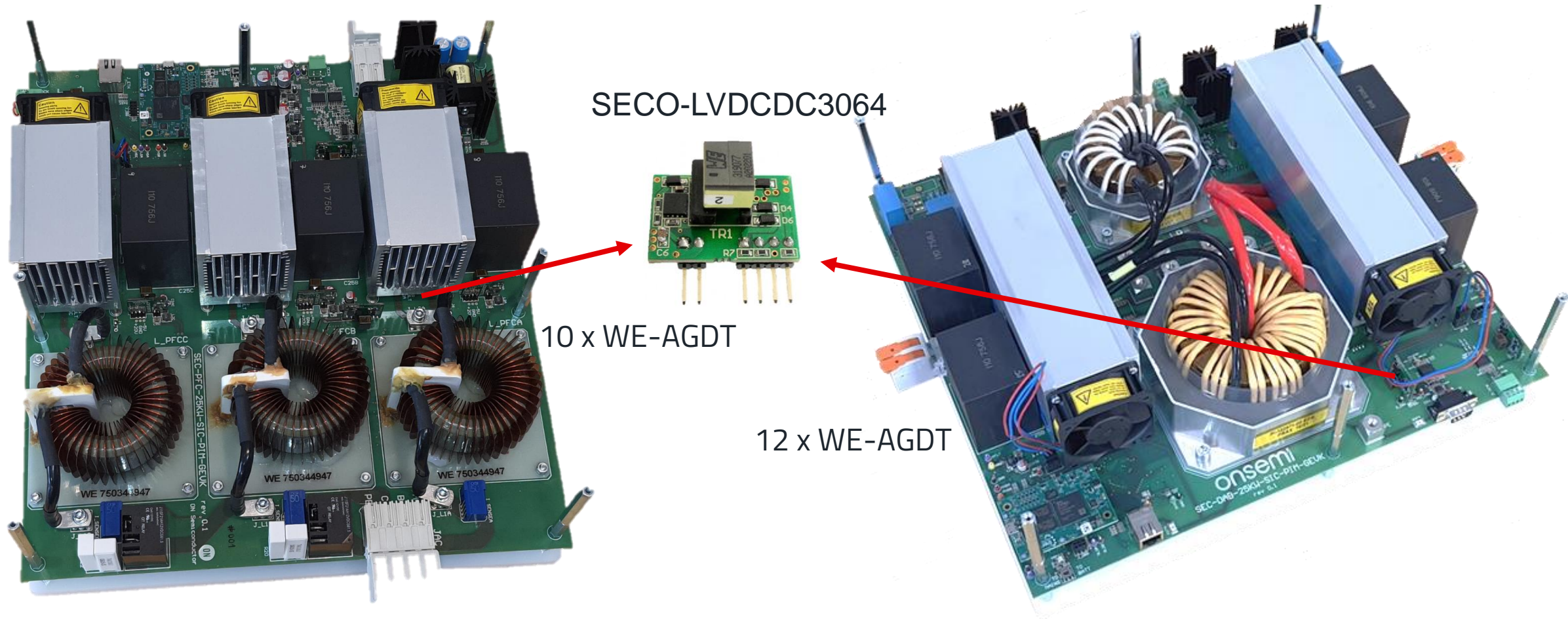
P/Ns and Values

P/N	Vin (V)	Vout1 (V)	Vout2 (V)	Vout3 (V)	Vaux (V)	Pout (W)
750319565	15	30				3
750319497	9-18	19	4			6
750319496	9-18	20	5			6
750319331	13	11.5				6
750319282	6-18	20	5	5	5	1.5
750319177	7.5	13				4.55
750319077	12-18	15	7.5	7.5	5	1.5
750318616	7-31	27			13	2.7

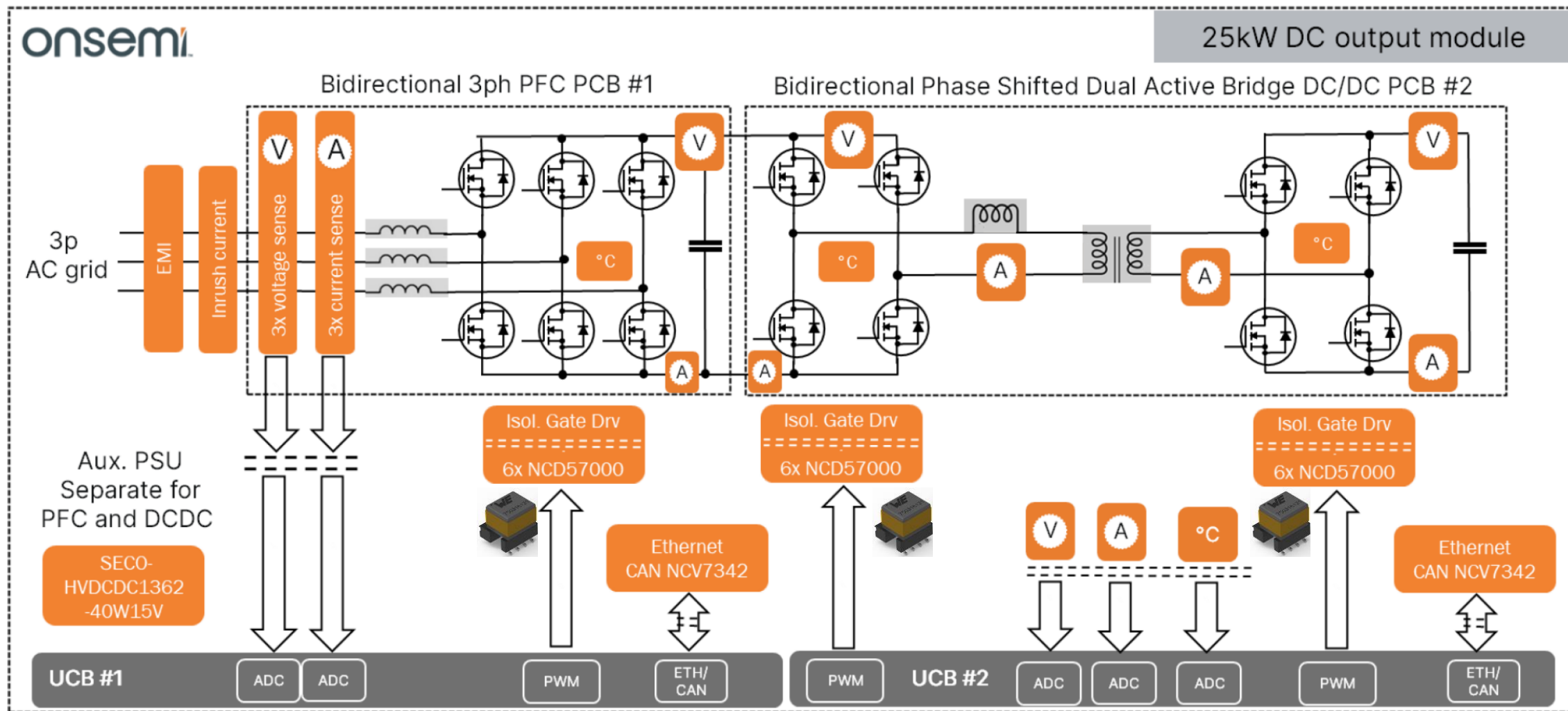


# APPLICATIONS

onsemi Reference Design – 25kW Fast Bidirectional Charger – PFC Stage



# APPLICATIONS

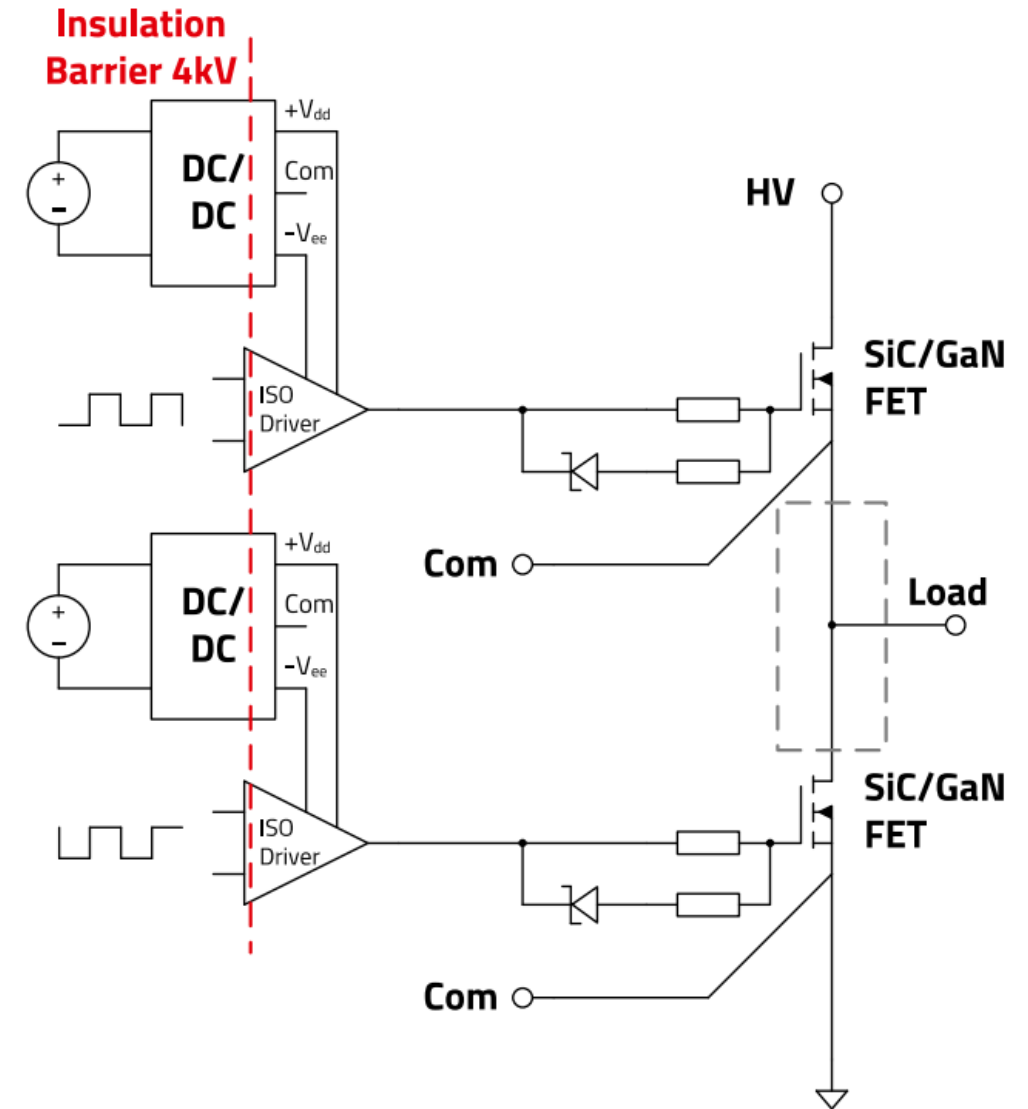


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# AUXILIARY GATE DRIVE TRANSFORMERS

Isolated supply for gate driving circuits

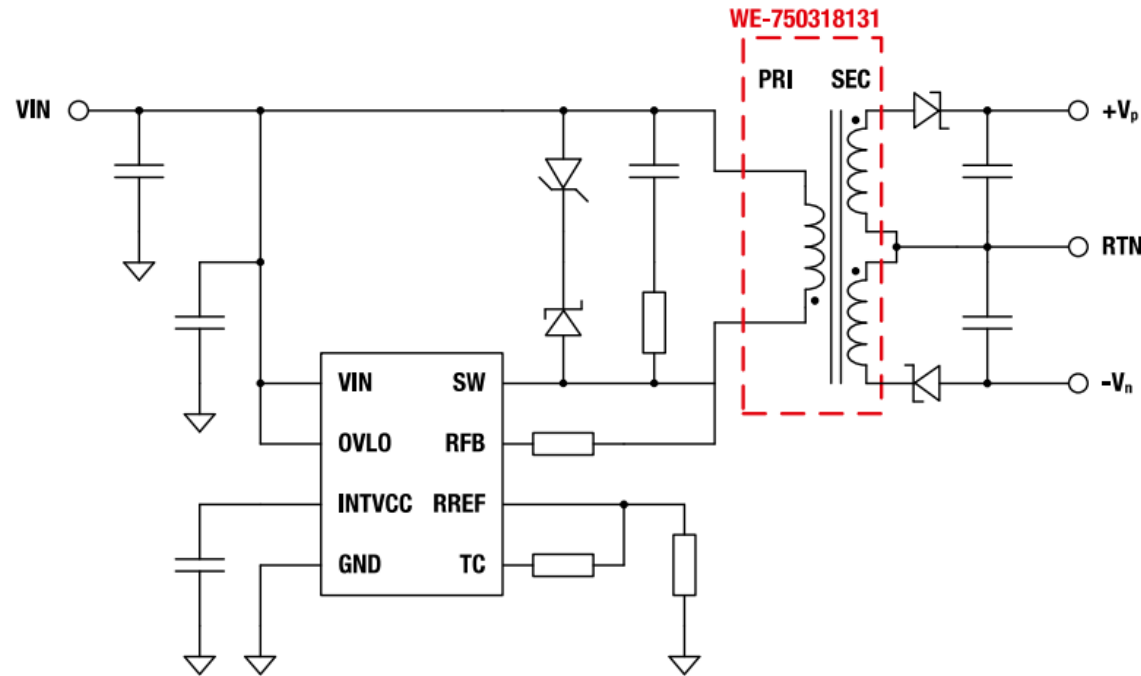
- Used to power the gate driving IC
- High voltage and high switch frequency – requirement for galvanic isolation, compliance with safety standards and EMI performance
- SiC MOSFETs
  - +15 V to +20 V to fully turn on
  - 0 V to -5 V to reliably turn off.
- GaN
  - +5 V to 0 V are required.
  - a small negative voltage to turn off



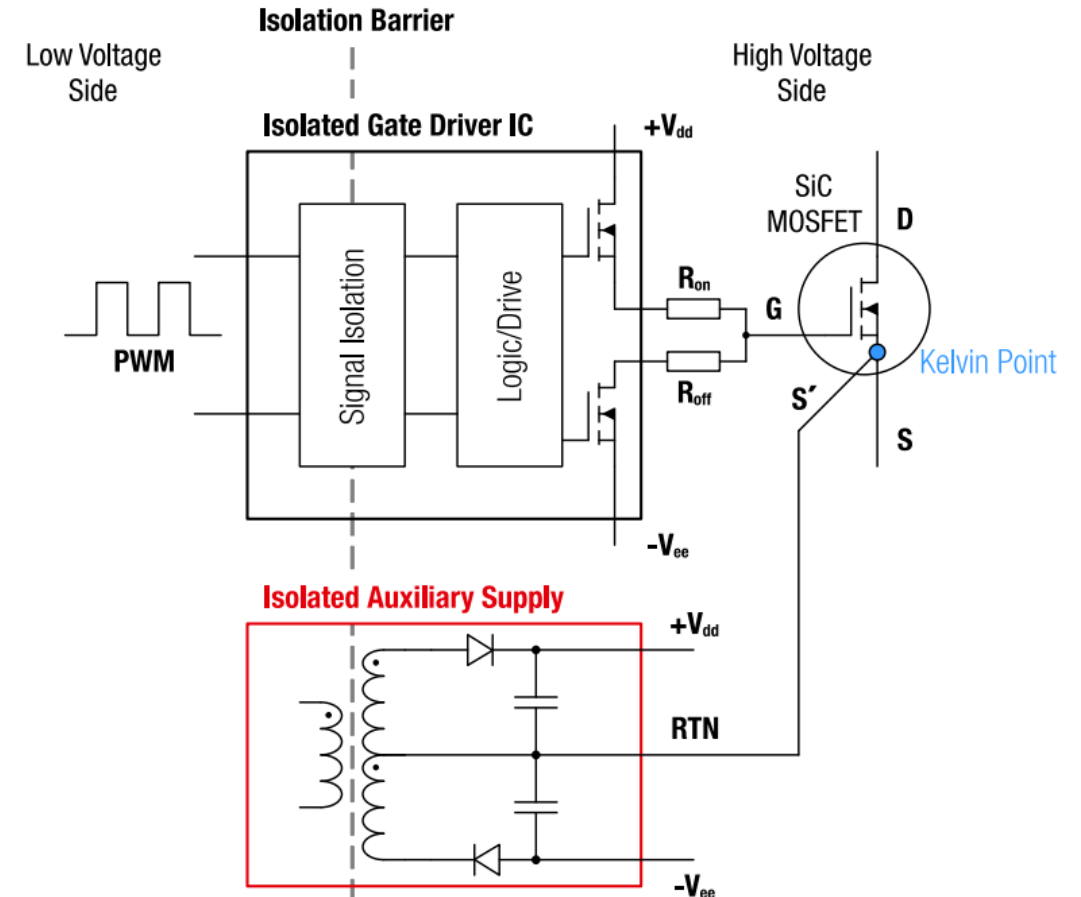


# AUXILIARY GATE DRIVE TRANSFORMERS

Typical Application – Bipolar auxiliary supply

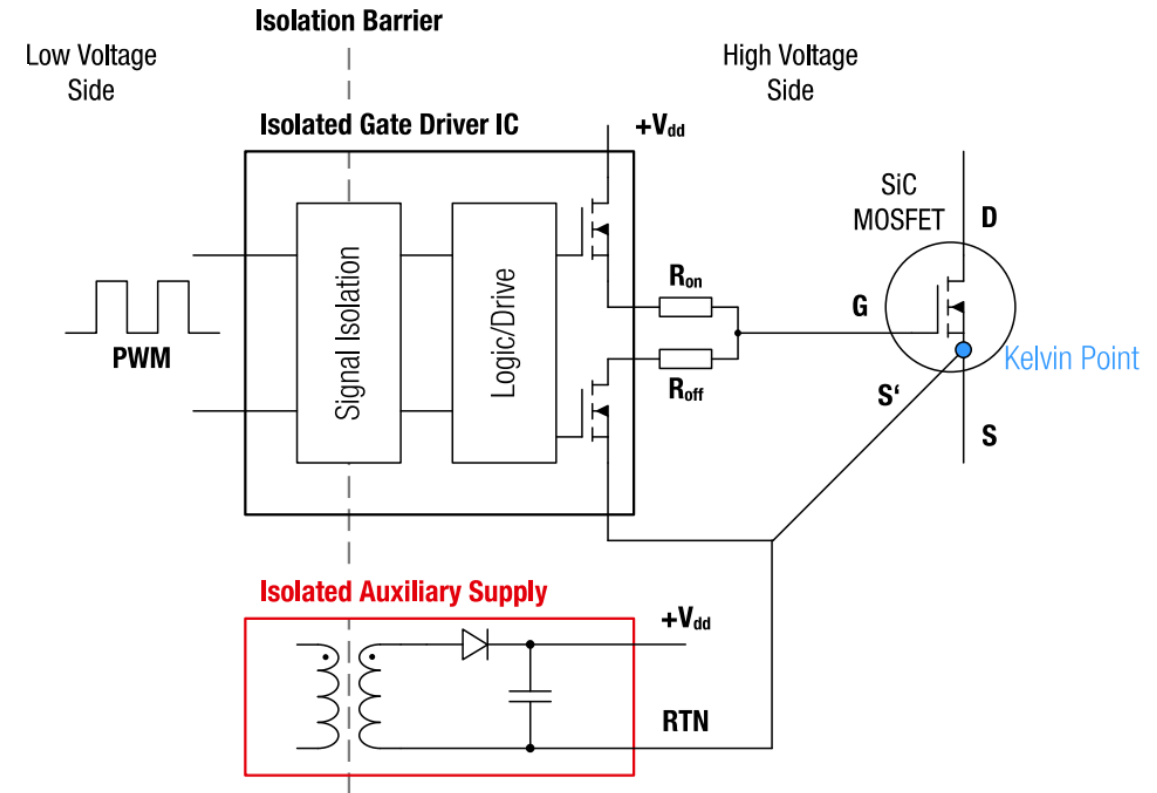
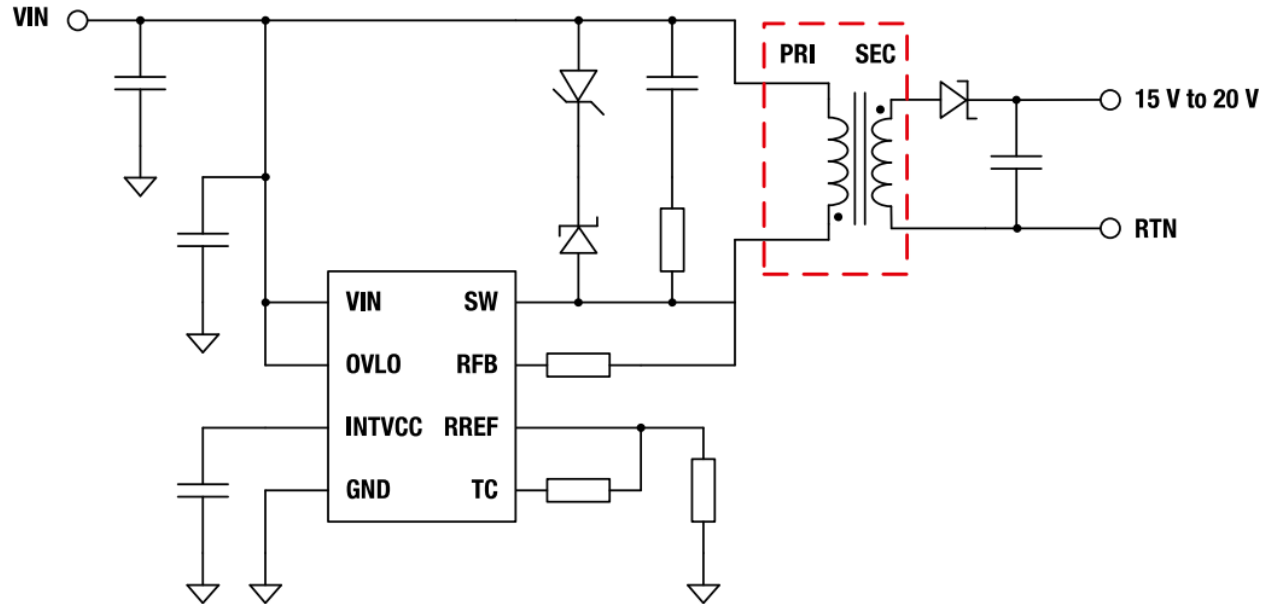


- Isolation provides not only functional safety, but provides robustness for gate driving and reduces noisy loop area, improving EMC (with good return implementation)



## AUXILIARY GATE DRIVE TRANSFORMERS

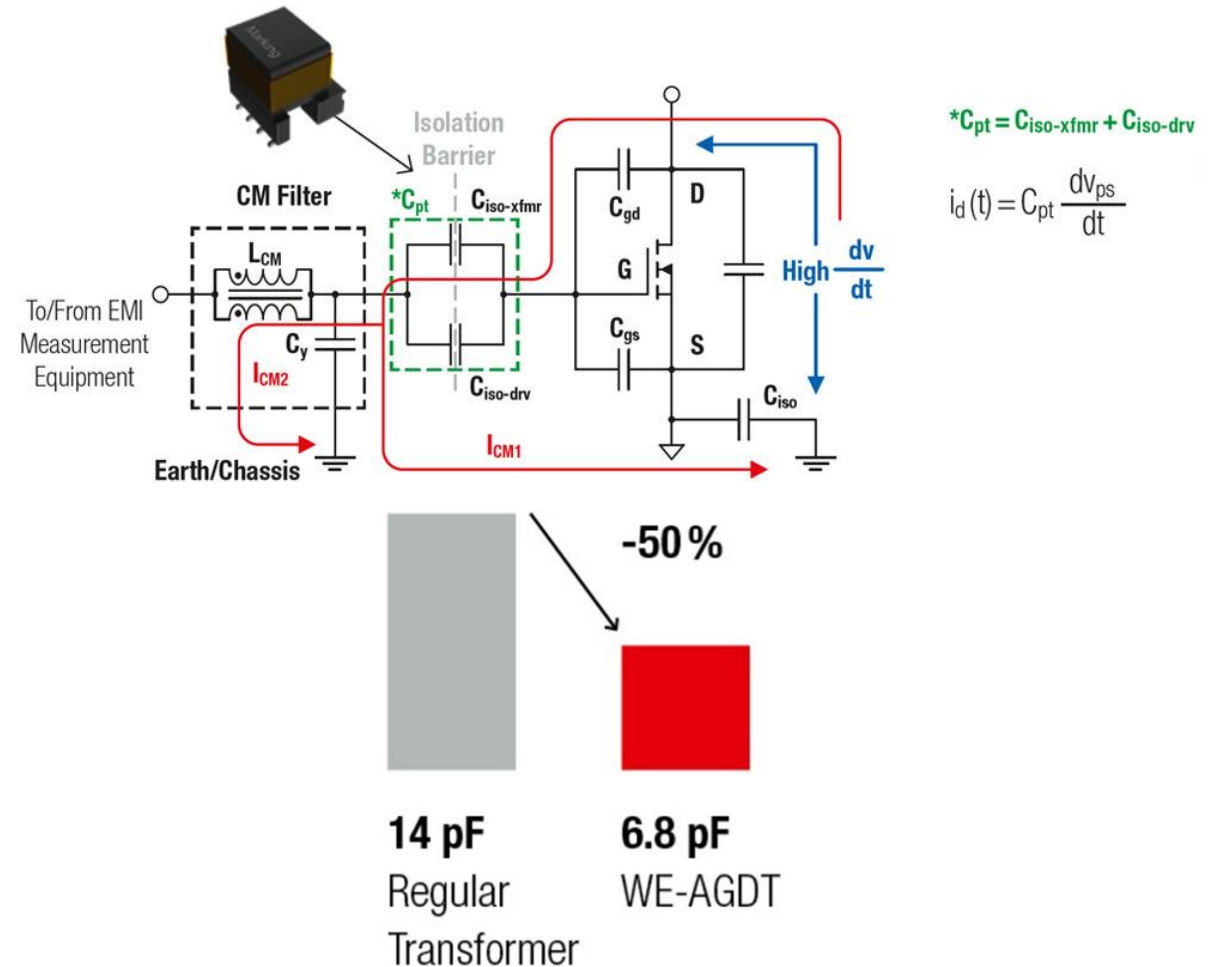
## Typical Application – Unipolar auxiliary supply



# AUXILIARY GATE DRIVE TRANSFORMERS

## Why Low Interwinding Capacitance Matters

- High  $dV/dt$  across device terminals while switching
  - High common-mode displacement currents generated
  - EMI Issues
- The capacitive parasitics are summed
  - Parasitic from the IC isolation barrier
  - Parasitic of the transformer isolation
- Very high CMTI



# NEW SERIES OVERVIEW

## Introducing WE-TORPFC

AEC – Q200  
Qualified



- 17x Catalogue parts in stock – No MOQ
  - Inductance: 118uH up to 720uH
  - Voltage: up to 1000VDC
  - High saturation current up to 105A
  - Temperature: -40°C up to 155°C
  - Outer diameter sizes: 53mm – 99mm
  - Height sizes: 28mm – 62mm
  - AEC-Q200 Grade 1
- Flat Wire Windings
  - Very low intra-winding capacitance
  - Minimized Skin Effect
  - Lower DCR
  - Mechanically stable
- Applications
  - External EV Chargers
  - Solar Inverters
  - Industrial/Medical AC-DC
  - Telecom PSU

# NEW SERIES OVERVIEW

## P/Ns and Values

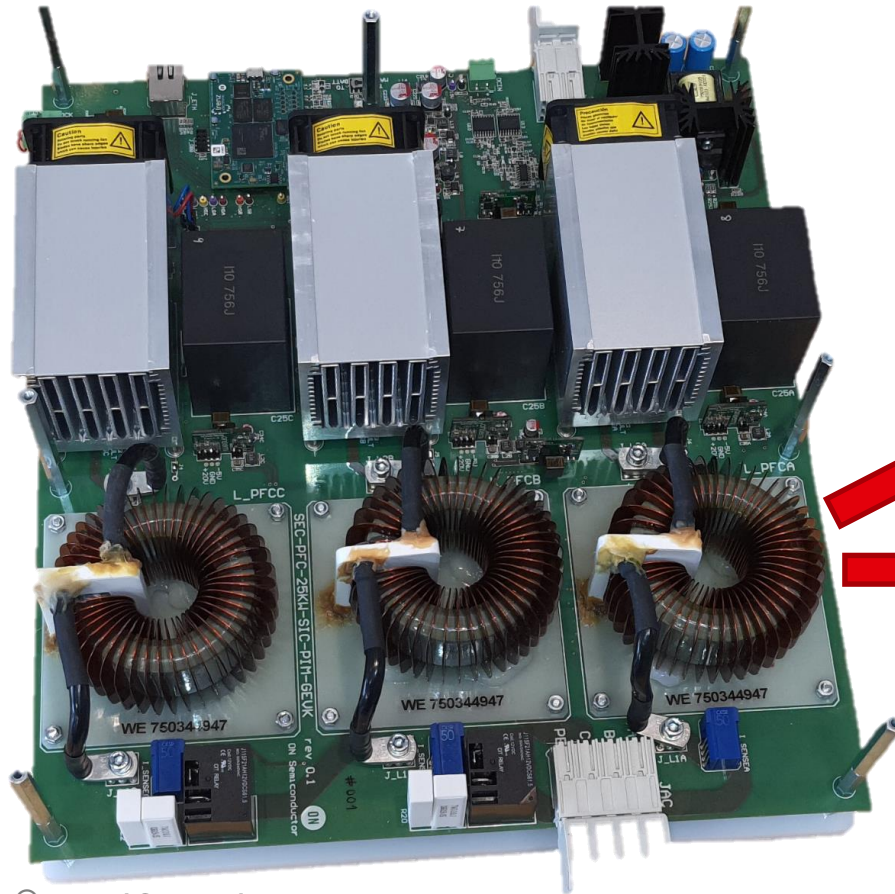
- Typical Inductance values
- Specification of rated current with airflow
- Smaller parts for same inductance and current compared to competition

Part Number	Max O.D. (mm)	Max Height (mm)	Inductance ( $\pm 20\%$ )	Max DCR (m $\Omega$ )	Rated Current (40°C Temp Rise)				Saturation Current (30% $\Delta L$ )
					No Air Flow	1 m/s Air Flow	2 m/s Air Flow	4 m/s Air Flow	
760800401	53	28	118 $\mu$ H	22	13.9A	19.7A	23.4A	27.5A	9.5A
760800403	53	47	355 $\mu$ H	35	12.3A	18.6A	22A	24.7A	9.5A
760800101	60	34	255 $\mu$ H	36	11.2A	16.1A	18.3A	21.7A	10.5A
760800102	60	54.5	510 $\mu$ H	55	9.8A	15A	17.4A	20.8A	10.5A
760800201	72	31	194 $\mu$ H	40	12.5A	16.5A	18.4A	21.9A	19A
760800202	72	45	389 $\mu$ H	50	11.5A	16.1A	18.2A	20A	19A
760800203	72	60	584 $\mu$ H	65	11.8A	16.8A	19.5A	22A	19A
760800301	99	62	180 $\mu$ H	20	24.5A	34A	42A	48A	43A
760801401	53	28	118 $\mu$ H	22	13.9A	19.7A	23.4A	27.5A	23A
760801403	53	47	355 $\mu$ H	35	12.3A	18.6A	22A	24.7A	23A
760801101	60	34	255 $\mu$ H	36	11.2A	16.1A	18.3A	21.7A	24A
760801102	60	54.5	510 $\mu$ H	55	9.8A	15A	17.4A	20.8A	24A
760801201	72	31	194 $\mu$ H	40	12.5A	16.5A	18.4A	21.9A	37A
760801202	72	45	389 $\mu$ H	50	11.5A	16.1A	18.2A	20A	37A
760801203	72	60	584 $\mu$ H	65	11.8A	16.8A	19.5A	22A	37A
760801301	99	62	180 $\mu$ H	20	24.5A	34A	42A	48A	105A
760801321	99	62	720 $\mu$ H	42	17A	23A	25.5A	32A	38A

# APPLICATIONS

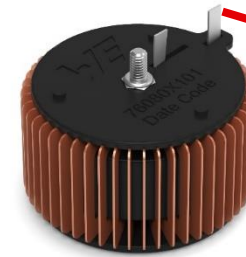
onsemi Reference Design – 25kW Fast Bidirectional Charger – PFC Stage

## 3-Phase Rectifier + PFC

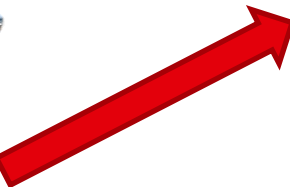


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P/N: 3 x 760801301 L:180uH; Isat:105A

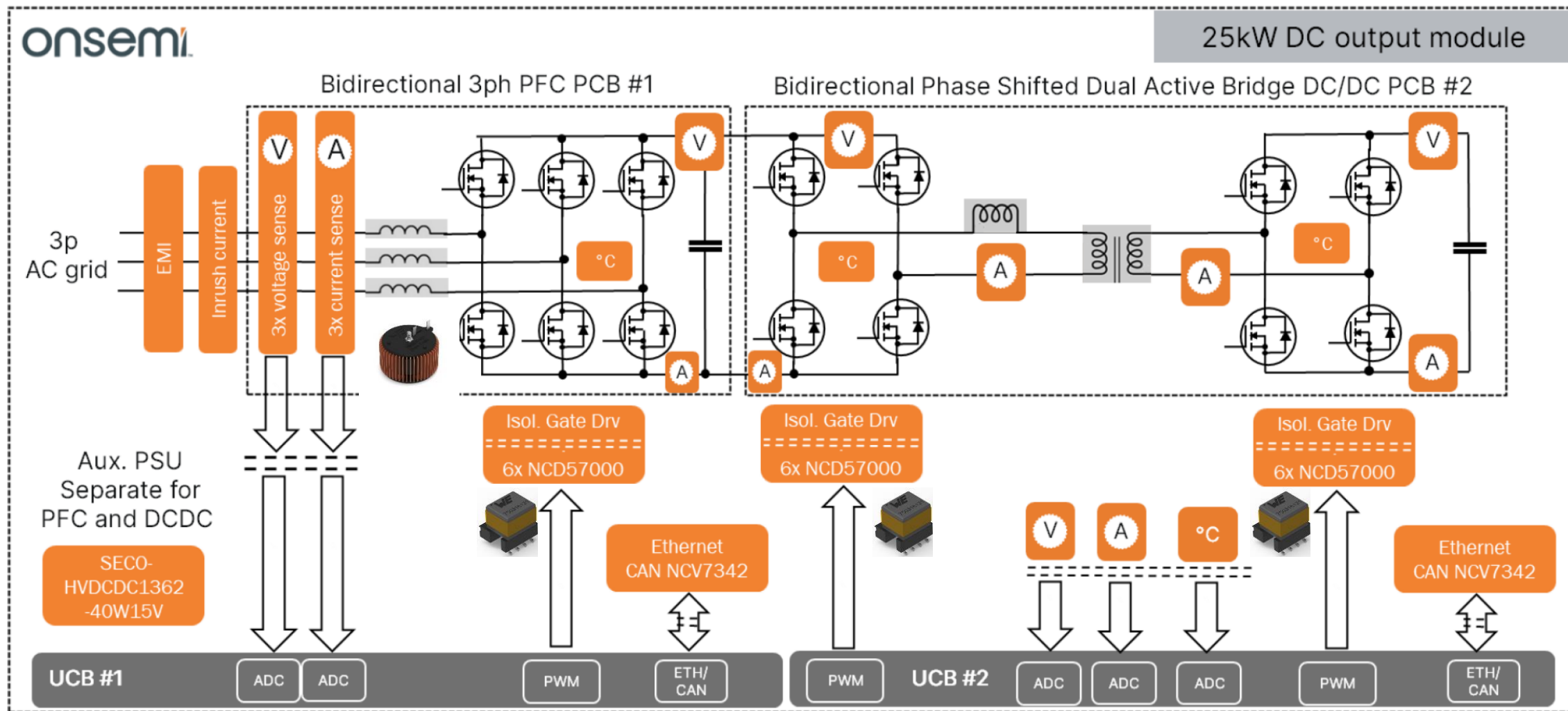


No flying leads, direct connection.  
Optimization of EMC



Initial samples for validation purposes

# APPLICATIONS



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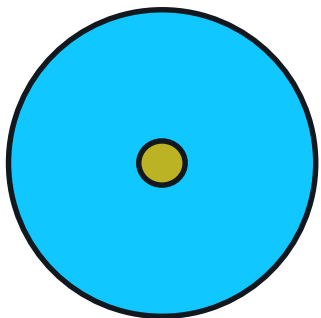
# WHY FLAT WIRE?



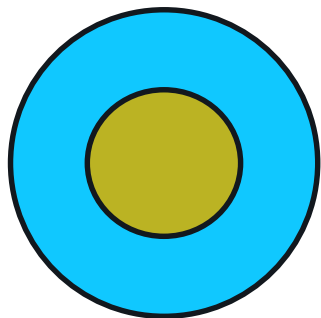
## Theory and measurements

- Skin Effect
  - Tendency of the current density in alternating current to become distributed towards the surface of the conductor
  - The higher the frequency, the more the current is pushed towards the surface
  - Effective cross-section is reduced resulting in higher AC resistance
  - Skin Depth – the depth at which current density is 37% of the value at the surface

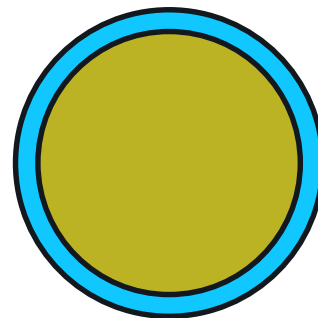
$$R \approx \frac{l\rho}{\pi D\delta}$$



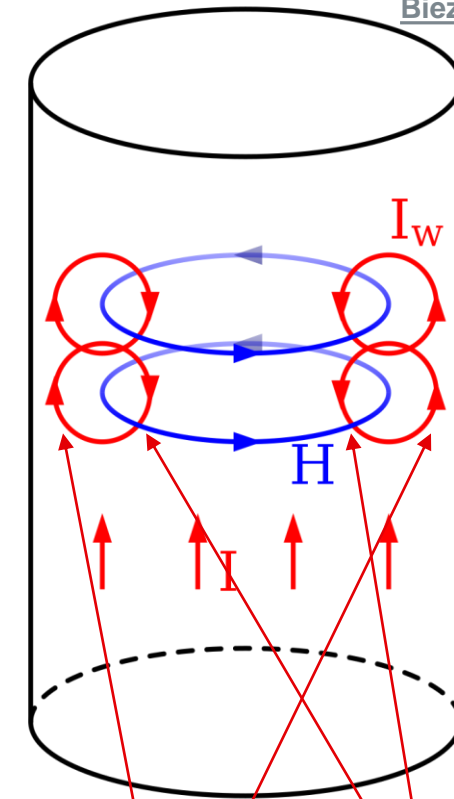
60Hz



1000Hz



400kHz



Biezl, Wikipedia

Current flow reinforced towards outer surface

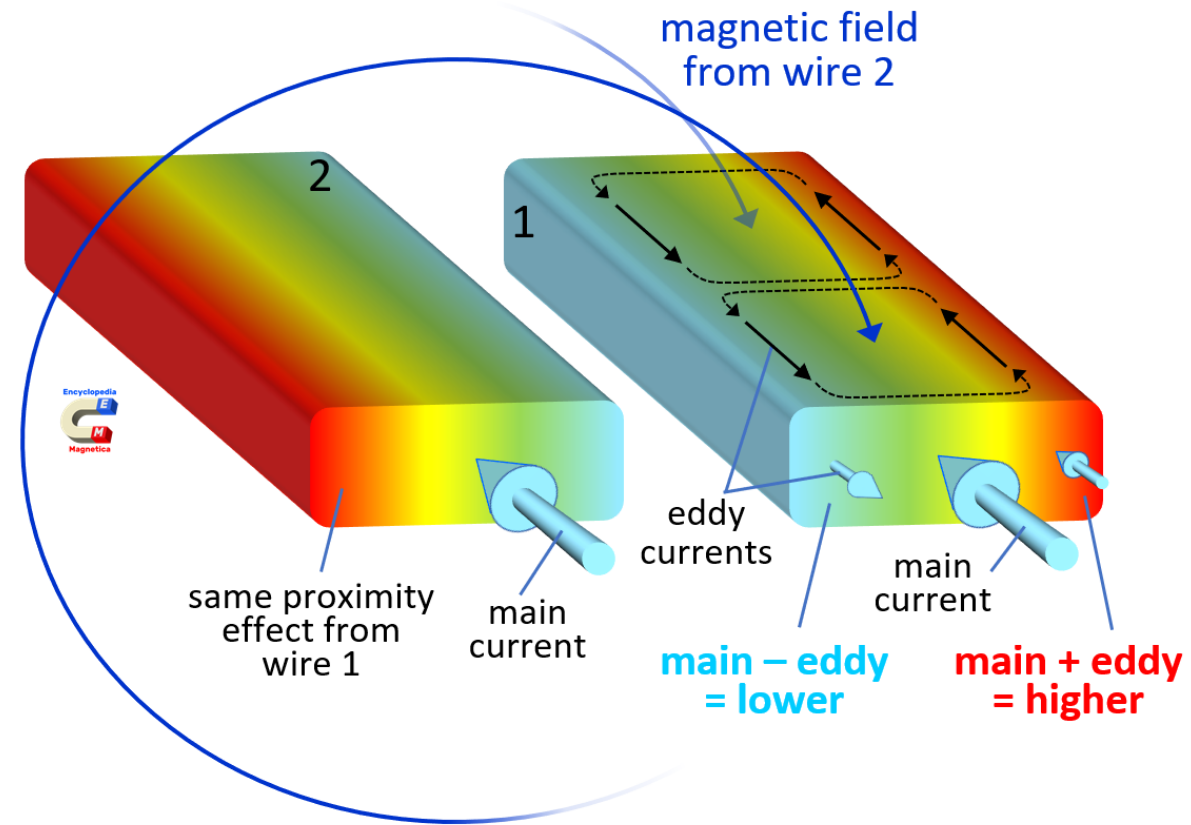
Eddy currents cancel current flow in center



# WHY FLAT WIRE?

## Theory and measurements

- Proximity effect
  - Current redistribution in conductors running in parallel and carrying alternating current
  - Conductors carrying current in same direction have current density distributed to the opposite sides
  - Conductors carrying current in opposite direction have current density distributed to the neighboring sides
  - Increase in AC resistance
  - Increased effect with higher frequency



Stan Zurek, Encyclopedia Magnetica

## WHY FLAT WIRE?

### Theory and measurements

- For this testing, 760800201 standard flat wire part was used and then hand wound a similar round wire sample. To wind a similar round wire part, the same core as 760800201 was used, same number of turns, and used equivalent sized round wires to obtain a similar DCR.



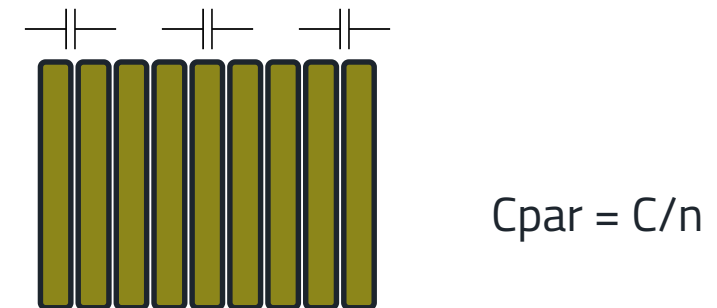
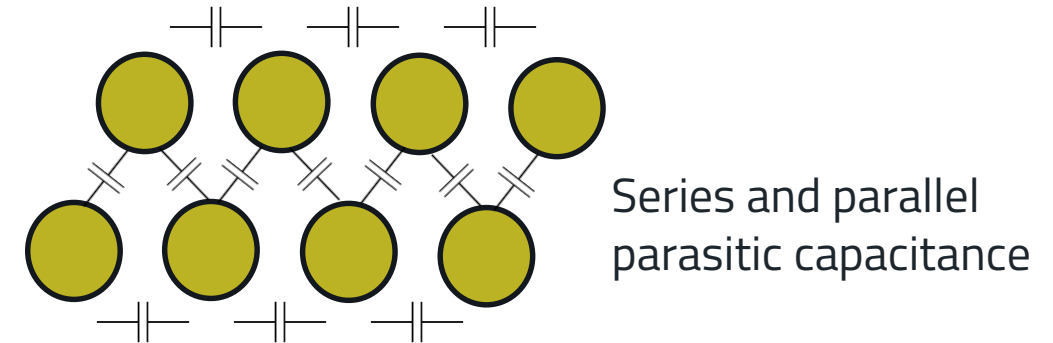
Characteristics	Round Wire	Flat Wire	760800201 Datasheet Specifications
Inductance (uH)	204	197	194
DCR (mΩ)	27.7	27.1	40mΩ max
Interwinding Cap (pF)	154	2.99	-
Rated I. ΔT=40K	11	12.4	12.4



## WHY FLAT WIRE?

### Capacitance matters

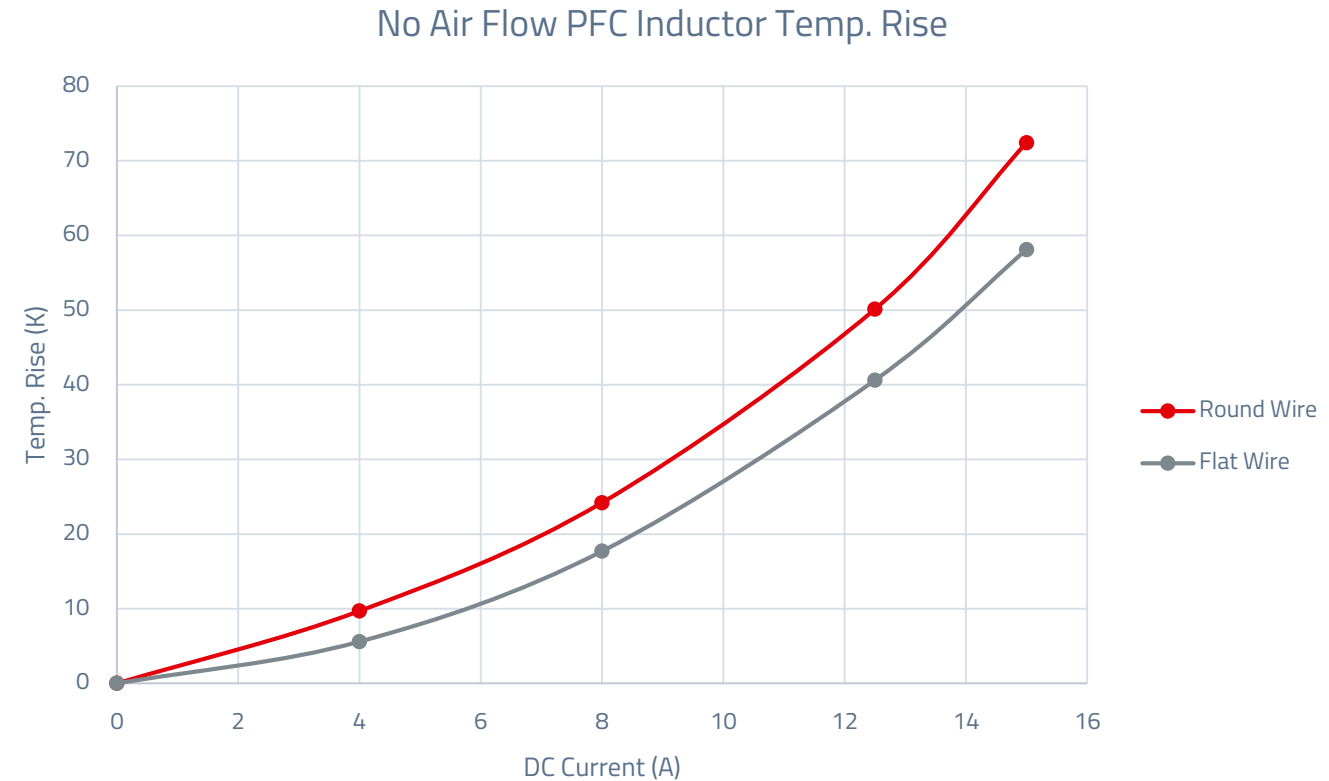
- Round conductor normal winding with all the parasitic capacitances shown – Parasitic capacitances are not just between adjacent horizontal layers, but also between vertical layers as well and between multiple inductors
- Flat wire, due to winding nature only has series parasitic capacitance



# WHY FLAT WIRE?

## Theory and measurements

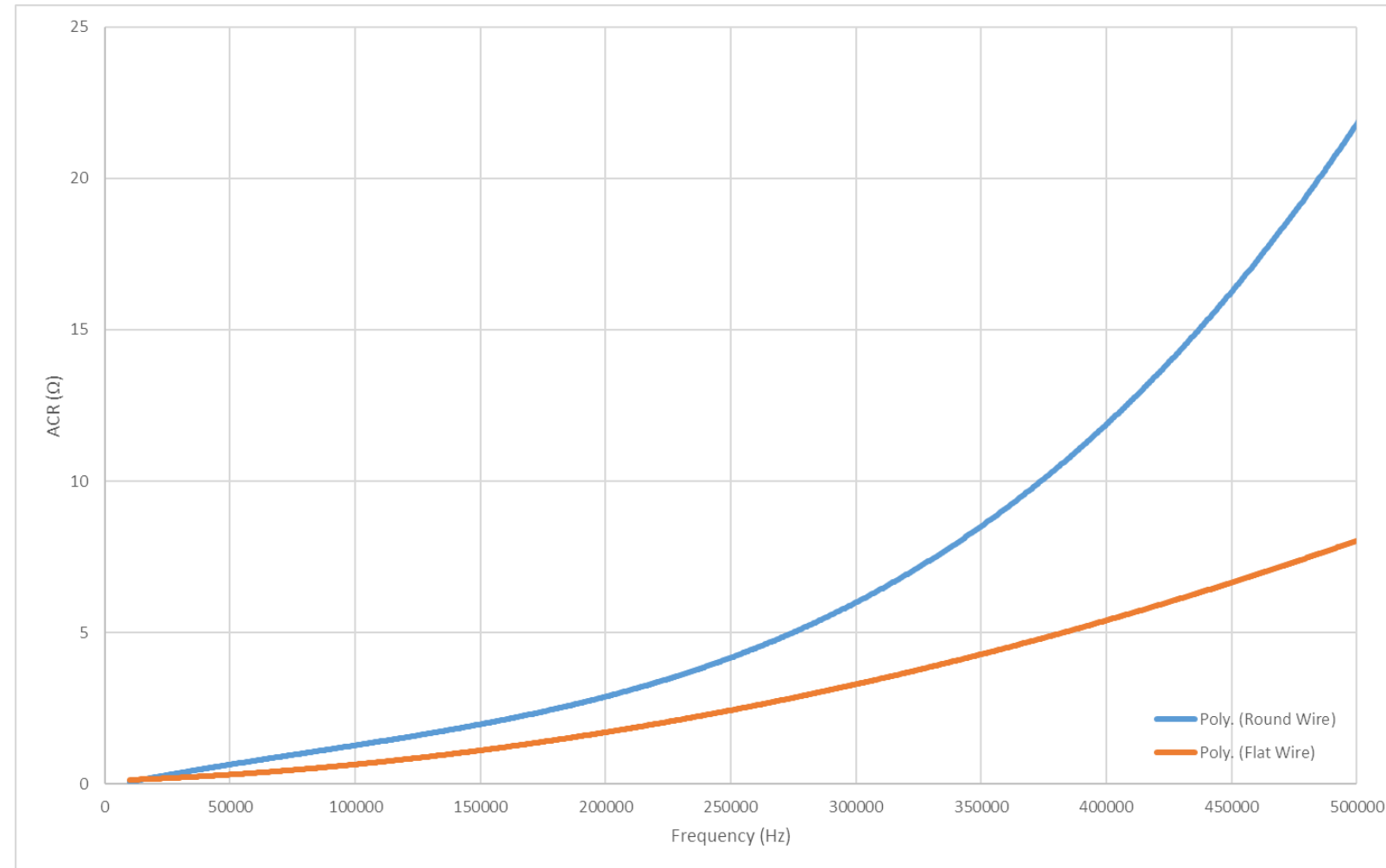
- For something as small as  $0.6\text{m}\Omega$  difference in DCR, at 15A we have 14.3 degrees difference.
- The difference comes from the better heat dissipation capabilities of the flat wire increased surface area.



# WHY FLAT WIRE?

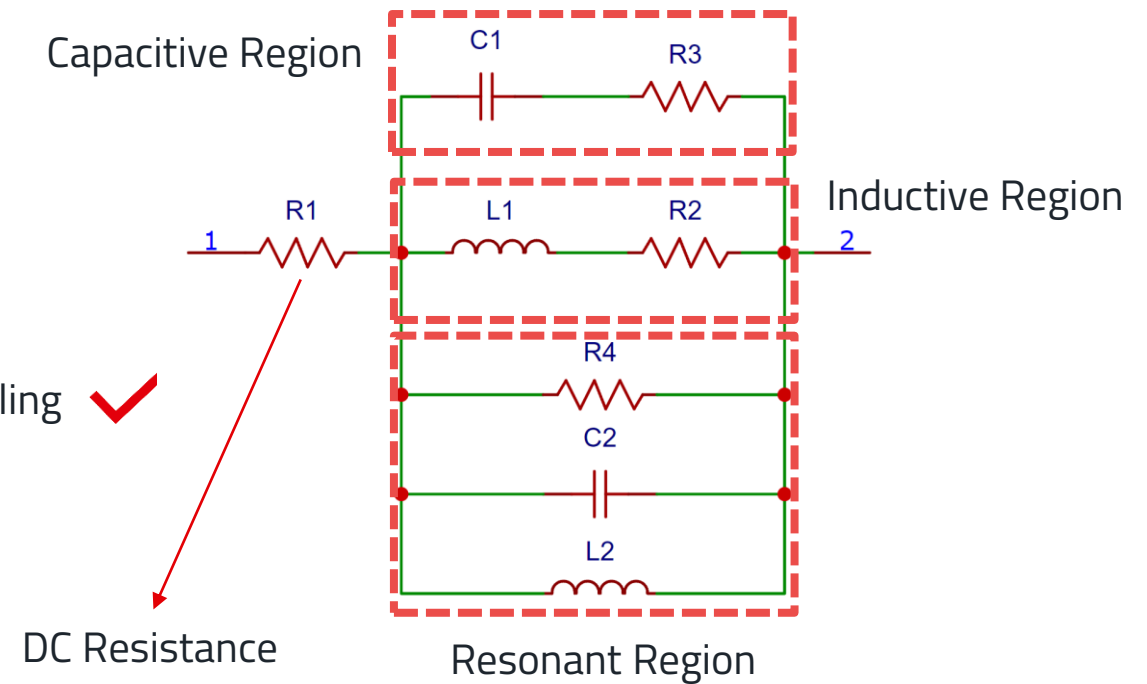
## Theory and measurements

- Difference in measured AC resistance between 10kHz to 50kHz
- Linearity in increase to 250kHz
- Exponential increase for round wire above 250kHz – remember skin effect.



## FLAT WIRE CONCLUSION

- Less interwinding capacitance – higher frequency ✓
- Lower DCR – lower losses ✓
- Skin effect reduced – reduced AC losses ✓
- Space between windings – proximity effect reduced + better cooling ✓
- Flat wire – higher mechanical stability ✓



*Real equivalent circuit of inductor*



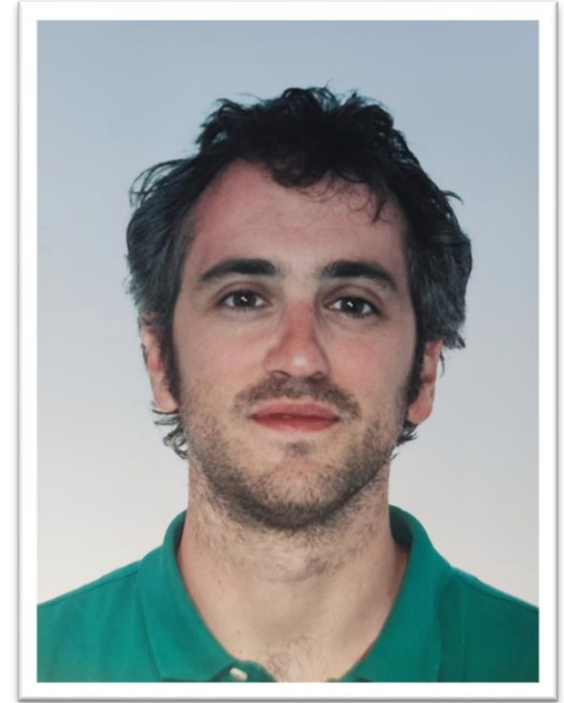
## DC-LINK CAPACITOR FOR THE 25 KW BIDIRECTIONAL CHARGER

Jon Izkue Rodriguez  
Hardware Engineer for Capacitors & Resistors  
Product Management

## JON IZKUE RODRIGUEZ

Hardware Engineer  
Capacitors & Resistors Product Unit

- Since 2018 in the Technical Engineering team in the Capacitors and Resistors Division at Würth Elektronik eiSos GmbH & Co. KG
- Background in Electronics Design & Measurement technology
- Writing Technical Application Documentation
- Definition and automation of measurement procedures
- Responsible for REDEXPERT Capacitor & Resistor Modules







WÜRTH  
ELEKTRONIK  
MORE THAN  
YOU EXPECT

onsemi™

## DC-LINK CAPACITOR FOR THE 25 KW BIDIRECTIONAL CHARGER FROM ONSEMI

- WCAP-FTDB Series Film Capacitors
- DC-Link Capacitor for the 25 kW bidirectional DC charger from Onsemi
- Characteristics
- Project Parts – Tailored to your needs
- Additional resources



# WCAP-FTDB: DC-LINK FILM CAPACITOR

Introducing new series WCAP-FTDB



## Würth Elektronik WCAP-FTDB DC-Link Film capacitors

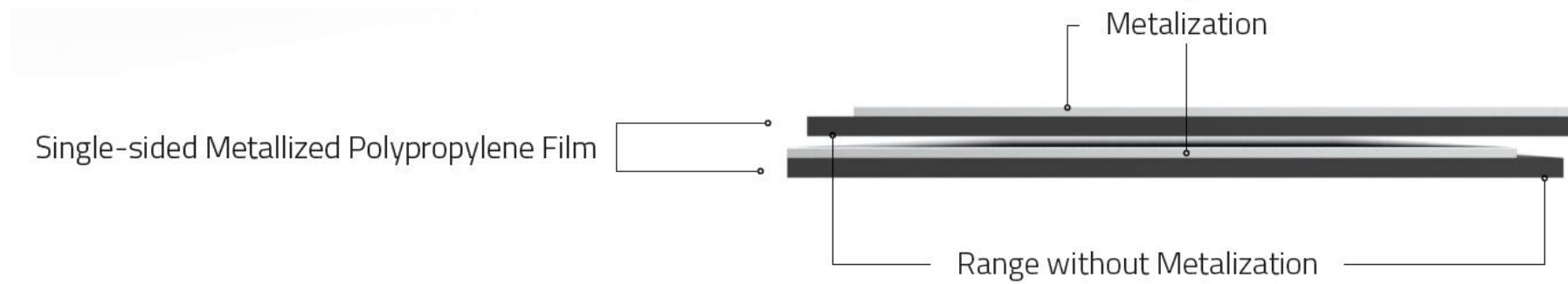
Boxed THT - MKP Film Capacitors

- 24x catalogue parts in stock – no MOQ
  - Capacitance: 1  $\mu$ F up to 75  $\mu$ F
  - Voltage: 500 V<sub>DC</sub> up to 1200 V<sub>DC</sub>
  - Temperature: -40°C up to 105°C
  - Pitch / Pin distance: 27.5, 37.5 and 52.5 mm

# WCAP-FTDB: DC-LINK FILM CAPACITOR

## Introducing new series WCAP-FTDB

- MKP: Polypropylene metallized film
  - High ripple current capability
  - Self-healing properties
  - Very long expected load life

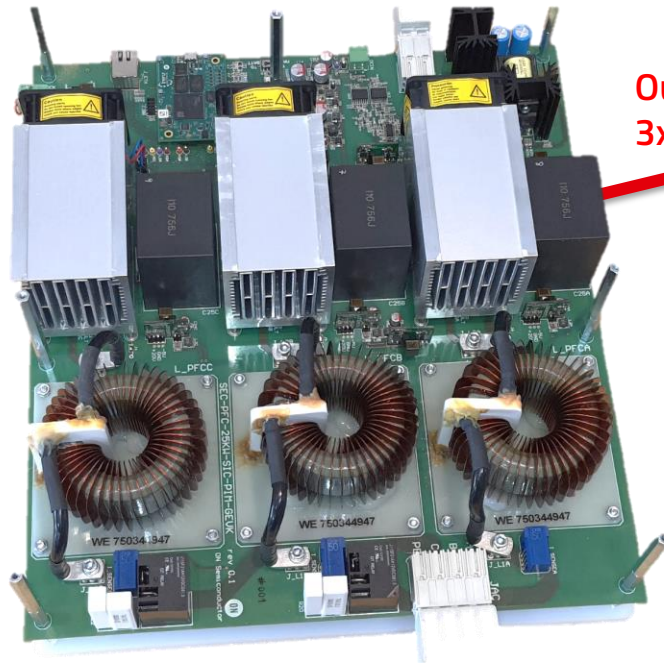




# WCAP-FTDB IN THE APPLICATION

## Onsemi Reference Design - 25 kW Fast DC Bidirectional Charger incl. PFC

### 3-Phase Rectifier + PFC



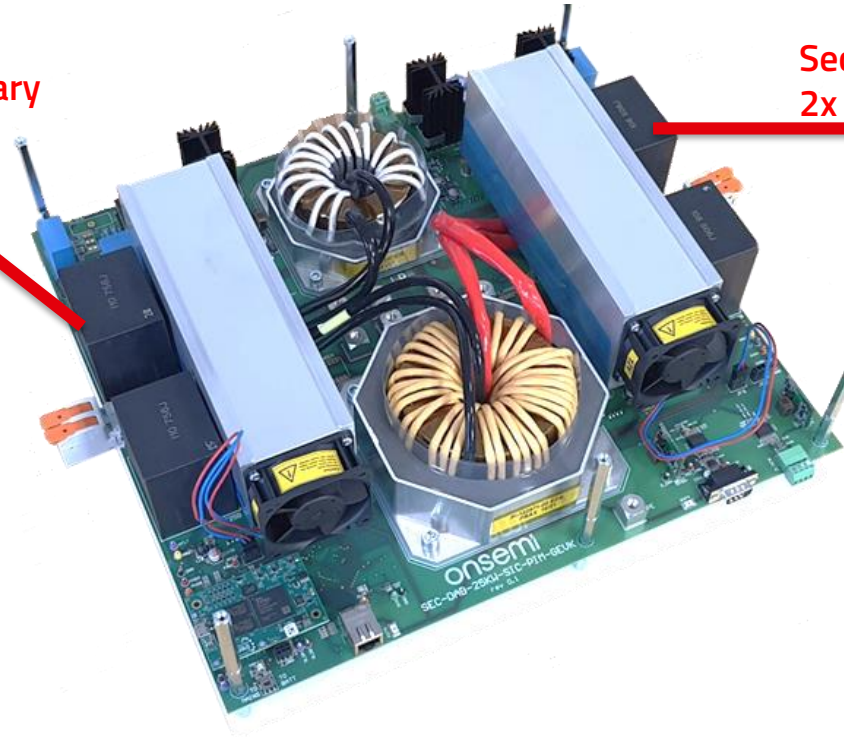
Output  
3x



WCAP-FTDB  
890724429010CS

75  $\mu$ F - 900 V

Primary  
2x



Secondary  
2x



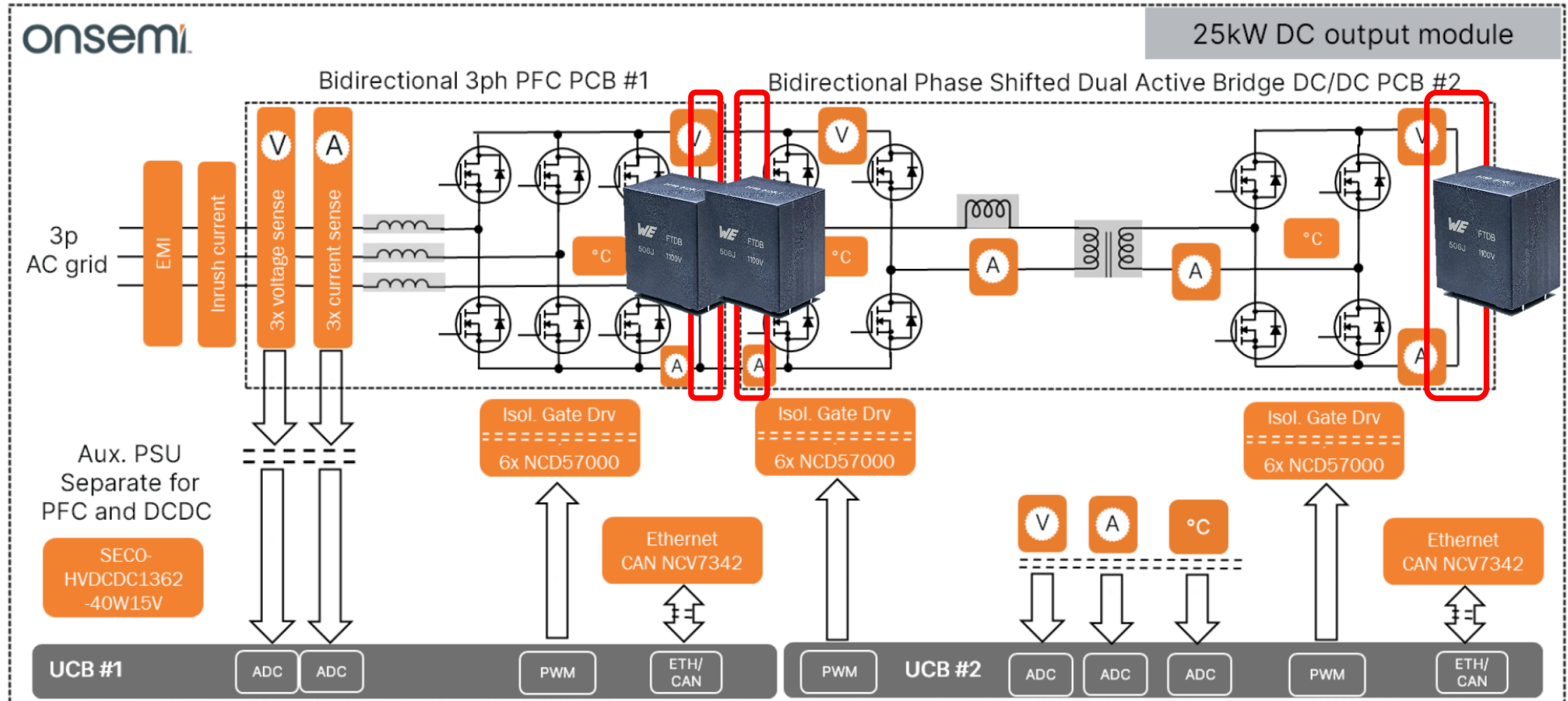
WCAP-FTDB  
890734429007CS

50  $\mu$ F - 1100 V

# WCAP-FTDB IN THE APPLICATION

WCAP-FTDB  
890724429010CS  
75  $\mu$ F - 900 V

WCAP-FTDB  
890734429007CS  
50  $\mu$ F - 1100 V



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# DC LINK CAPACITOR TECHNOLOGIES

## Onsemi Reference Design - 25 kW Fast DC Bidirectional Charger incl. PFC

### Film DC Link Capacitors



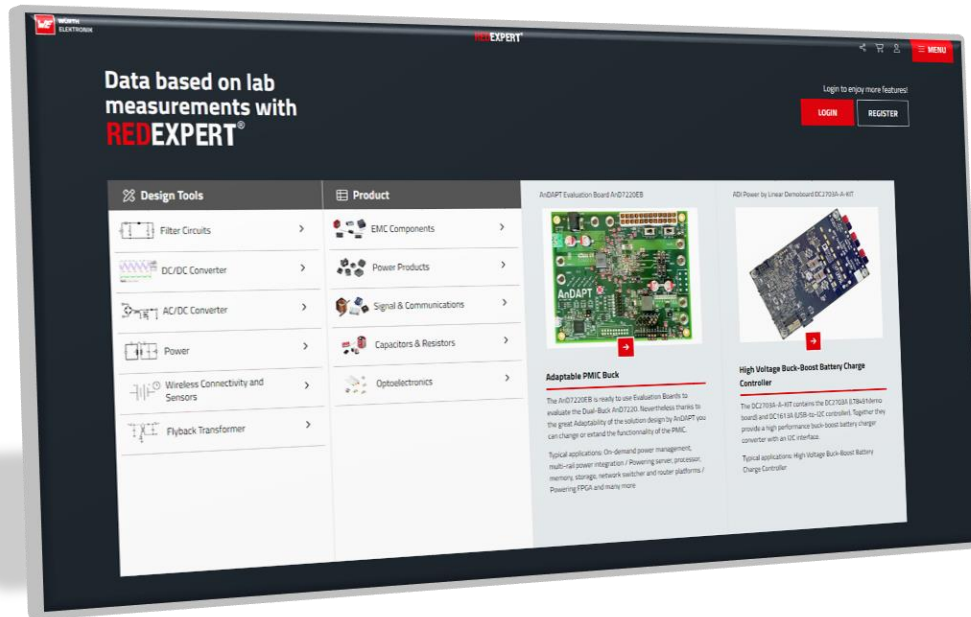
- Rated voltages up to 1,200 V
  - Perfect for the used SiC Modules
- Very low ESR - High RMS current capabilities
  - Ripple current: several  $A_{RMS}$  per  $\mu F$
- Low capacitance may cause high voltage ripple
- No liquid inside - long storage and load life
- Self-healing properties

### Aluminum Electrolytic Capacitors



- Rated voltages up to 650 V
  - Series connection necessary!
- Relatively high ESR internal resistance
  - Depends on the part 1 mA/ $\mu F$ ...20 mA/ $\mu F$  or higher
- High capacitance values
  - Highest capacitance per volume ( $\mu F / mm^3$ )
- Get large bulk capacitance for low voltage ripple

Free browser platform optimized for component selection

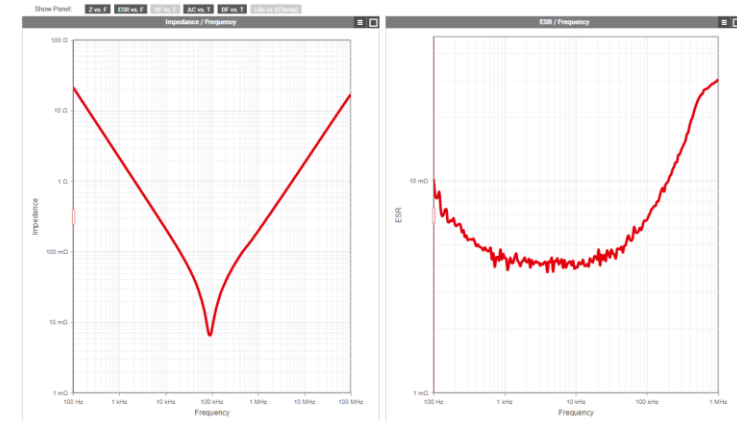


Scan for  
DC-Link  
Module!



Find all standard specifications and following curves:

- Z vs Freq. (Impedance spectrum)
- ESR vs Freq.
- D ( $\tan \delta$ ) vs Freq.
- Capacitance vs Temperature
- D ( $\tan \delta$ ) vs Temperature
- Temperature /Voltage vs Lifetime (Derating curve)



## PROJECT PARTS – TAILORED TO YOUR NEEDS

- 24x catalogue parts available from stock
  - Free samples service
  - No MOQ – Minimal order quantity
  - Available measurements, simulation models and CAD files
- Project parts available for orders with MOQ
  - Additional configurations available in the family:
    - Capacitance 0.68  $\mu\text{F}$  to 100  $\mu\text{F}$
    - Voltage Rating 500 V<sub>DC</sub> to 1200 V<sub>DC</sub>
    - Pitch: 27.5 mm, 37.5 mm or 52.5 mm
    - Height from 18 mm to 65 mm
    - Other terminal options
  - Measurements, Simulation and CAD files may be provided after order and production cycle
  - Additional features available\*



[eiCapHotline@we-online.de](mailto:eiCapHotline@we-online.de)



## MORE INFORMATION

- E-mail:  
[Jon.Izkue.Rodriguez@we-online.com](mailto:Jon.Izkue.Rodriguez@we-online.com)
- [Webinar \(Youtube\) - DC-Link Capacitor, Specification and Application](#)
- [Webinar \(Youtube\) - The Effects of Harsh Environmental Conditions on Film Capacitors](#)
- [Application Note: Impedance Spectra of Different Capacitor Technologies](#)
  - ***Register for our next Webinar about this topic on 11.07.2023***



Scan to go to  
Webinar  
registration!

# Questions

& Answers



Online Catalogue  
WCAP-FTDB



Online Catalogue  
PFC Chokes